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Novel Design of Syntheses and Materials for Stable and Efficient Perovskite Photovoltaics

장을 및 공정 설계를 통한 장수명 고효율의 페로브스카이트 광전소자 구현

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Novel Design of Syntheses and Materials for Stable and Efficient Perovskite Photovoltaics

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Abstract

Global energy demand mainly relies on fossil fuels, petrochemical, and nuclear energy. Those causes the emission of greenhouse gas and radioactive waste, threatening the mankind. Alternatively, renewable energy is slowly replacing the demand of current energy sources, yet the portion of renewable energy production is very small. Solar cell is one of the most promising energy production by converting incident light into electricity, expecting the solution for energy problem without environmental issues. In order to make solar cell compatible in an energy market, high power conversion efficiency (PCE) at low production cost with high durability should be satisfied. Moreover, solar cells must applicate into various situations in human lives, such as wearable devices, improving the efficiency of energy production. Therefore, understanding and developing the science of material and device must be advocated to commercialize the solar cells in a broad market.

Researchers have been explored the sufficient material and device structures to robust the potential of solar cell. Especially, utilization of thin-film semiconductor in solar cell has explored widely due to its superior optoelectronic properties. Among the various types of thin-film semiconducting materials, organometallic perovskite has demonstrated amorous potential due to the nature advantage of proper bandgap, absorption coefficient, and diffusion length. Moreover, synthesis and fabrication of material and layer are inexpensive and facile, promising for the large scale production. However, the organic site of organometallic perovskite (methylamonium (MA) or formamidinium (FA)) is highly reactive under light, heat, and water, making device insufficient for the commercial
use. Despite the issues of organometallic perovskite, electron and hole transporting materials in solar cell take expensive and complex processes, limiting the potential of organometallic perovskite photovoltaics. Therefore, further modification steps for materials and device should be proposed to overcome the current limitation.

In Chapter 1, basic understanding of organometallic perovskite and solar-cell physics are discussed. It includes theoretical study of material design and functional mechanism of solar cells by physicochemical perspectives, and discuss the pioneered researches to improve the optoelectronic property of solar cells. Moreover, general principles of material and device degradation with established strategy will be handled to follow the general principle of organometallic perovskite research.

In Chapter 2, ideal process and synthesis of organometallic perovskite solar cells are covered. In early 2014, chlorine-doped perovskite has gather the much attentions due to the passivating effect of chlorine in a perovskite lattice. Chlorine (Cl) doping not just improve the PCE of the device, but also enhance the stability. However, the detailed reaction process wasn’t defined clearly, which could provide an additional room for the further optimization. To understand the reaction steps and formation of Cl-doped perovskite, different synthesis and deposition techniques were studied. Therefore, the extent of reaction was controlled to observe the intermediate phases during the reaction, and we have further utilized them to create the highly stable and efficient material synthesis. At the end, stable solar cell was fabricated by using newly created perovskite.

In Chapter 3, synthesis and fabrication of electron transporting (n-type) material are discussed. Metal oxide are widely used as an n-type layer, and
deposition and synthesis require complex processes to make a high quality film. Vacuum and solution depositions are two typical methods for $n$-type layer, and individual deposition has problem on a rough transparent-conducting oxide (TCO) substrate ($n$-$i$-$p$ structured device). Also, the growth of perovskite can be hindered by the quality of $n$-type layer, requiring further improvement. Therefore, combinational strategy of vacuum and solution processes has conducted to provide the extreme compact $n$-type layer, improving the performance of device.

In Chapter 4, degradation issue of organometallic perovskite under light, heat, and water are investigated. Organic site of organometallic perovskite roles the main terminal for degradation, which will be studied and modified to resolve the instable behavior of organometallic perovskite (methylammonium (MA) or formamidinium (FA)). Also, optoelectrical property of organometallic perovskite will be discussed to develop the ideal methodology of organometallic perovskite design. Especially, organic cation with multiamine based aromatic compound is ideally utilized as a solute of organometallic perovskite. Distinctive structure of aromatic compound obtains delocalized $\pi$-bonds exhibiting superior optoelectronic property with sensational stability to resolve the stabilities of material and device. Therefore, chemistry and design theory of organometallic perovskite will be discussed deeply.

In Chapter 5, stability and cost of $n$-type layer (metal oxide) are discussed. In most of cases, metal oxide produces photocatalytic reaction during the illuminating condition, leading unexpected degradation of solar cells. Therefore, progress for developing efficient and stable electron transporting materials will be
handled with the detailed study. Moreover, metal oxides require high temperature process to obtain the proper electron mobility, requiring high cost to fabricate. Therefore, low-temperature synthesis of metal oxide for efferent device will be handled in this chapter.

In Chapter 6, combinational strategy of perovskite chemistry are covered. Organometallic perovskite chemistry obtains organics, post transition metal, and halides, where the organic site role as the main terminal for perovskite degradation. Organics share hydrogen bonding within a lattice, which is weak enough to break under high energy or polar environment. Therefore, the interaction of organics is fully engineered by substituting alkali metal to form a covalent bond and low-dipole organics to stabilize the material. While the material has engineered, optoelectrical and thermodynamic property of organics and metal are once more understood to create the efficient and stable device.

**Keywords:** Solar cells, organometallic perovskite, compositional engineering, solvent, cation, anion, electron transporting material, hole transporting material, stability, polymer, metal oxides, hybrid material, deposition process, recombination, defect, electronic trap.

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Table of Contents

Abstract
Table of Contents
List of Figures
List of Tables
Chapter 1. Overview of Perovskite Photovoltaics
  1.1. Operation Mechanism of Solar Cells
  1.2. Application and Potential of Perovskite in Solar Cells
  1.3. Depositions of Perovskite Photovoltaics.
  1.5. References
Chapter 2. Solvent and Intermediate Phase as Boosters for the Perovskite Transformation and Solar Cell Performance
  2.1. Introduction
  2.2. Experimental Section
  2.3. Results and Discussion
  2.4. Conclusions
  2.5. References
  3.1. Introduction
  3.2. Experimental Section
  3.3. Results and Discussion
  3.4. Conclusions
  3.5. References
Chapter 4. An Aromatic Diamine Molecule as the A-Site Solute for Highly
Durable and Efficient Perovskite Solar Cells

4.1. Introduction
4.2. Experimental Section
4.3. Results and Discussion
4.4. Conclusions
4.5. References

Chapter 5. Origins of Efficient Perovskite Solar Cells with Low-Temperature Processed SnO$_2$ Electron Transport Layer

5.1. Introduction
5.2. Experimental Section
5.3. Results and Discussion
5.4. Conclusions
5.5. References

Chapter 6. Triamine-Based Aromatic Cation as a Novel Stabilizer for Efficient Perovskite Solar Cells

6.1. Introduction
6.2. Experimental Section
6.3. Results and Discussion
6.4. Conclusions
6.5. References

Appendix: List of Publications and Presentations

A.1. Publications (International)
A.2. Presentations (International and Domestics)

국문 초록
감사의 글
List of Figures

Chapter 1.

Fig. 1-1. Energy-band diagram of a silicon $p$-$n$ junction solar cell.

Fig. 1-2. Solar spectrum and the energy production of light-induced solar cells.

Fig. 1-3. $J$-$V$ characteristic and factors in solar cells.

Fig. 1-4. Plots for recorded solar cell efficiencies and $S$-$Q$ limit.

Fig. 1-5. (a) 4-terminal, (b) 2-terminal, (c) four-terminal optical spectral splitting, and (d) four-terminal reflective tandem solar cells.

Fig. 1-6. Schematic representation of the organometallic perovskite with species A, B and X.

Fig. 1-7. Band diagram of perovskite solar cells with the different device architectures and materials.

Fig. 1-8. Absorption coefficient and relation between Urbach energy of various solar cell materials. Charge mobility and defect of perovskite.

Fig. 1-9. Tunable bandgap of perovskite by halide exchange.

Fig. 1-10. (a) Vacuum, (b) and (c) solution process, and combination of vapor and solution depositions of perovskite film.

Fig. 1-11. Thermodynamic nucleation of precursor-processed perovskite (MAPbI$_3$).

Fig. 1-12. (a-c) Water-induced degradation of perovskite layer, and (a,b,d) the passivation layer to block the water damage.

Fig. 1-13. Evolution of LBIC mapping of perovskite at the different temperature and relative humidity.
Fig. 1-14. Degradation mechanism of metal doped Spiro-OMeTAD.

Fig. 1-15. Degradation mechanism of photocatalyzed metal oxide and perovskite.

Fig. 1-16. Light-induced degradation of perovskite

Chapter 2

Fig. 2-1. Schematic illustration of the MAI in ethanol or iso-propanol diffusing into the PbCl$_2$-wetted mesoporous-TiO$_2$ (mp-TiO$_2$). The blocking-layer is coated on SnO$_2$:F (FTO).

Fig. 2-2. Time-dependent optical variation for the PbCl$_2$ films in the MAI/ethanol or MAI/iso-propanol solution.

Fig. 2-3. MAPbI$_3$ conversion using a methanol solvent: (a) SEM images for the MAPbI$_3$ film in different regions (20-min dipping sample), and (b) optical observations in every 5 min.

Fig. 2-4. SEM images of (a) MAPbI$_3$ and (b) $J$-$V$ curve from the 20-mg/mL MAI/iso-propanol solution.

Fig. 2-5. Solvent effects on MAPbI$_3$ using ethanol or isopropanol. (a) SEM images of MAPbI$_3$ using ethanol, (b) MAPbI$_3$ using iso-propanol, and (c) PbCl$_2$ on mp-TiO$_2$. The average cuboid size is shown for MAPbI$_3$ by ethanol or iso-propanol.

Fig. 2-6. The dependence of MAPbI$_3$ perovskite solar cells using the MAI in an ethanol or iso-propanol solution. (a) EDS mapping for iodine and
chlorine in the synthesized MAPbI₃ with an ethanol (top) or isopropanol (bottom) solution. (b) Cross-sectional SEM image of a MAPbI₃ perovskite solar cell from the MAI/ethanol solution. (c) X-ray diffraction of MAPbI₃. (d) Absorption spectra for the synthesized MAPbI₃. (e) J-V characteristics of the MAPbI₃ perovskite solar cells. (f) Degradation of solar cells synthesized by ethanol or isopropanol for the as-fabricated cells and cells after 30 days.

Fig. 2-7. X-ray diffraction from various MAI/ethanol dipping times on the PbCl₂ film.

Fig. 2-8. Device reproducibility of MAPbI₃ perovskite solar cells from the reactions 1, 2, 3, 4, and iso-propanol.

Fig. 2-9. Stability of MAPbI₃ perovskite solar cells from the reactions 1, 2, 3, and 4 for 30 days. The corresponding data by iso-propanol (RXN 1) are also shown.

Fig. 2-10. Reaction intermediates and mechanism analysis by X-ray diffraction measurements. (a) Reaction 1 (left), reaction 4 (middle), and PbI₂ precursor (right) with various concentrations of MAI in an ethanol solution. (b) Mechanisms of reaction 1 (PbCl₂ + 3 MAI → MAPbI₃ + 2 MACl). The MAI and ethanol diffuse into the outer PbCl₂ layer, which converts PbCl₂ into PbI₂ and MACl. Additional MAI from the solution converts the synthesized outer PbI₂ into MAPbI₃, and MACl reacts with the inner PbCl₂ transforming into MAPbCl₃. The synthesized MAPbCl₃
ion-exchanges with I\(^-\) for the full MAPbI\(_3\) and MACl to complete the reaction.

Fig. 2-11. Schematic illustration of the experimental procedure. Various ratios of PbCl\(_2\): MAPbCl\(_3\) were initially deposited on the substrate, and then the MAI-dissolved ethanol solution was utilized to synthesize MAPbI\(_3\).

Fig. 2-12. The film quality dependence of MAPbI\(_3\) for the reactions 1, 2, 3, and 4. (a) SEM images of the precursor and MAPbI\(_3\), (b,c) X-ray diffraction for the precursor and MAPbI\(_3\), and (d) absorption spectra of MAPbI\(_3\) by reactions 1, 2, 3, and 4.

Fig. 2-14. Time-dependent optical variation for the reactions 1, 2, 3, and 4 in a MAI/ethanol solution.

**Chapter 3**

Fig. 3-1. Concentration control of a TiO\(_2\) solution on the sputter-deposited TiO\(_2\) to optimize the performance of perovskite solar cell (with hole-transporting material).

Fig. 3-2. Schematics and energy diagrams of the solar cells with various TiO\(_2\) blocking layers deposited by sputter, solution, or double-step method. Red arrows indicate the recombination phenomena of carriers.

Fig. 3-3. Cross-sectional and plan-view SEM images of blocking-layer TiO\(_2\) by (a) sputter, (b) solution, and (c) double-step deposition.
Fig. 3-4. Performance optimization of the perovskite solar cell by varying the thickness of sputter-deposited TiO₂.

Fig. 3-5. Transmittance from the differently deposited blocking layers (before the solar-cell fabrication).

Fig. 3-6. Schematics with top-view SEM images of MAPbI₃/mp-TiO₂/BL-TiO₂/FTO: (a) sputter, (b) solution, and (c) double-step deposition.

Fig. 3-7. Topography maps and RMS values of the perovskite films obtained from atomic-force microscopy (AFM).

Fig. 3-8. Crystallinity and optoelectrical properties of MAPbI₃ devices on various blocking layers: (a) X-ray diffraction, (b) transmittance of MAPbI₃ films, (c) J-V curves (a scan rate of 10 V/s), and (d) EQE spectra of the perovskite solar cells.

Fig. 3-9. Device reproducibility of MAPbI₃ perovskite solar cells from the sputtering, solution, and double-step deposition (as shown in Table 3-3).

Fig. 3-10. Comparison of the impedance spectroscopy for differently fabricated perovskite solar cells (sputter, solution, and double-step methods) at various voltages (0.1, 0.3, 0.5, and 0.7 V under dark condition).

Fig. 3-11. Nyquist plot and equivalent circuit model (under dark condition) of the perovskite solar cells with different blocking layers (the inset presents a magnified plot for the double-step blocking layer).

Fig. 3-12. Recombination resistance ($R_{rec}$) of the perovskite solar cells under dark condition.
Chapter 4

Fig. 4-1. Schematic illustration for structural transformations in the imidazole incorporated perovskite. Perovskite with 100% imidazole cation leads 2.9 eV of high band gap, which is not sufficient for solar-light absorber. Therefore, imidazole is soluted in CH$_3$NH$_3$PbI$_3$ to satisfy the requirements for perovskite solar cells.

Fig. 4-2. FTIR spectra and x-ray diffraction analysis for the characterization of IZ$_2$PbI$_4$.

Fig. 4-3. Absorbance and work function of IZ$_2$PbI$_4$ on a TiO$_2$/FTO substrate.

Fig. 4-4. X-ray diffraction of the IZ$_{0.1}$MA$_{0.9}$PbI$_3$ film.

Fig. 4-5. Identification of perovskite alloying with large IZ contents (0%, 25%, 50%, 75%, and 100%): (a) 150°C-annealed FAPbI$_3$, and (b) 100°C-annealed MAPbI$_3$.

Fig. 4-6. Characterization of imidazole-alloyed perovskite films with varying alloying contents of 0.0%, 2.5%, 5.0%, and 7.5%. (a) Peak shifts in X-ray diffraction scans and effect on the lattice parameter ($a = b$ in tetragonal phase). (b) Relative transmittance of imidazole-alloyed MAPbI$_3$ through FTIR.

Fig. 4-7. X-ray-diffraction characterization of IZ-alloyed perovskite (0.0%, 2.5%, 5.0%, and 7.5%) in MAPbI$_3$. 

List of Figures
Fig. 4-8. Transmittance of imidazole-alloyed MAPbI₃ using FTIR (with major peaks of MAPbI₃ labeled).

Fig. 4-9. Atomic ratio of carbon and lead by EDS at different IZ contents in MAPbI₃, compared to the ideal concentration (dashed line).

Fig. 4-10. Optical and electronic characteristics of imidazole-alloyed MAPbI₃ films. (a) Band gap change, (b) grain-size distributions, (c) electrical conductivity, and d) work function.

Fig. 4-11. SEM images of different IZ contents in MAPbI₃.

Fig. 4-12. Electrical conductivity of films with various IZ contents in MAPbI₃ (with 100% indicating IZ₂PbI₄).

Fig. 4-13. Device performance and stability Test. (a) J–V curves (scan rate of 10 mV s⁻¹) and b) EQE spectra of imidazole-alloyed MAPbI₃. (c) Degradation of devices up to 30 days when cells are stored in air (≈ 55% humidity and dark). (d) Steady-state current for a 1000 s time scale to confirm the light- and voltage-induced degradation of the solar cells. e) Heat-induced degradation of devices under 100°C for 6 h. (f) J–V curve of the champion device in this study (with 2.5% imidazole, and forward and reverse J–V shown as dotted and solid lines, respectively) and its steady-state current (at 0.90 V) using a SnO₂/ITO substrate.

Fig. 4-14. J-V curves for various contents of imidazole-alloyed MAPbI₃ (dotted and solid lines for forward and reverse scans, respectively) on TiO₂/FTO substrates.
Fig. 4-15. Reproducibility of perovskite solar cells for various contents of imidazole-alloyed MAPbI$_3$ on TiO$_2$/FTO substrates.

Fig. 4-16. X-ray-diffraction characterization of perovskite films after 30 days in air.

Fig. 4-17. $J$-$V$ curves of fresh vs. aged (100°C for 6 h) devices.

Fig. 4-18. Thermogravimetric analysis (TGA) for characterization of the thermal stability of perovskite powders.

Fig. 4-19. Cross-sectional and plan-view SEM images for fresh and thermal-induced devices (100°C for 6 h).

Fig. 4-20. $J$–$V$ curve and steady-state current results with a large active area of 2 cm$^2$ (2.5% imidazole) by using a SnO$_2$/ITO substrate.

Chapter 5

Fig. 5-1. Device performance versus SnO$_2$ annealing temperature. (a) $\eta$, (b) $V_{OC}$, (c) $FF$, (d) $J_{SC}$, and (e) $HI = (\eta_{rev} - \eta_{fast})/\eta_{rev}$ of solar cells as a function of SnO$_2$ annealing temperature. Each data point demonstrates the representative device of one experimental batch. (f) $J$-$V$ curves of champion cells at room temperature and 120°C with the cell geometry by SEM (CsFAMA = Cs-doped (FA$_{0.83}$MA$_{0.17}$)Pb(I$_{0.83}$Br$_{0.17}$)$_3$).

Fig. 5-2. IPCE spectra of the perovskite solar cells. The IPCE measurements of PSCs with various SnO$_2$ annealing temperatures. The integrated JSC are indicated.
Fig. 5-3.  $J-V$ curve of the champion cell for each SnO$_2$ annealing temperature. Solar cells are examined by (a) reverse scan and (b) forward scan, respectively. The corresponding cell parameters are referred in Table 5-1.

Fig. 5-4.  X-ray diffraction patterns of perovskite solar cells, with and without HTL/Au. XRD patterns of (a) full devices and (b) perovskite films, fabricated on a SnO$_2$ layer annealed at various temperatures. Peaks are indexed assuming perovskite crystal in a cubic structure. The diamond and asterisk symbols represent the peak positions of PbI$_2$ and ITO, respectively.

Fig. 5-4.  SEM images of perovskite film surfaces. Surface morphology of perovskite film deposited on a SnO$_2$ layer annealed at (a) RT, (b) 80°C, (c) 120°C, (d) 160°C, and (e) 200°C.

Fig. 5-6.  Basic characterizations of SnO$_2$ thin films. (a) Cross-sectional SEM image of the device (ITO/SnO$_2$/CsFAMA/spiro/Au) with a thickness estimation of SnO$_2$ layer. (b) Planar SEM image and (c) AFM topography of bare ITO and ITO/SnO$_2$ surfaces. The AFM images are shown in the same color scale. For (b) and (c), SnO$_2$ films are characterized before and after annealing at 120°C.

Fig. 5-7.  Morphological features and electrical properties of SnO$_2$ films. Surface topography of (a) bare ITO substrate, and (b-f) SnO$_2$ layer annealed at different temperatures. The AFM images are shown in the same color scale. (g) Roughnesses by peak-to-valley and root-mean-squared values
as a function of annealing temperature with bare ITO as a reference. (h) Electric conductivity of SnO₂ thin films.

Fig. 5-8. Energy level diagram of SnO₂ electron-transport layer. (a) Secondary electron edge and (b) valence-band maximum of SnO₂ layer at each annealing temperature (as measured by UPS). (c) Tauc plot of SnO₂ films for the bandgap energy \( E_g \). The blue arrow indicates the shift of bandgap as the annealing temperature increases (Detailed fitting parameters for panels a-c are in Table 5-3). (d) Schematic band diagram of each SnO₂ layer with the perovskite as a reference.

Fig. 5-9. Effects of annealing temperature on the electronic trap states. (a) Capacitance-frequency plot and (b) trap distribution spectra of solar cells. (c) Trap density per volume \( N_t \) and \( V_{oc} \) of each solar cell. \( N_t \) is obtained by fitting the trap density state in (b) using a Gaussian function. (d) Schematics for the role of interfacial traps in recombination.

Fig. 5-10. Thermal stability of perovskite solar cells. Stability of encapsulated perovskite solar cells with SnO₂ ETL annealed at 120°C, stored in 85°C environment with 85% relative humidity (RH) in dark. Two devices are shown in a normalized PCE (reverse scan).

Chapter 6

Fig. 6-1. Schematics and characterization of perovskite films. (a) Illustration for 1,2,4-triazole alloying in the triple-cation perovskite, and (b) the observed peak shift
in XRD by alloying process. (c) Typical functional groups (C=N and N=N) in the 1,2,4-triazole alloyed perovskite by FTIR analysis.

**Fig. 6-2.** Characterization of perovskite films. (a) XRD with the ITO peak to confirm the clear peak shifting due to the alloying (Fig. 6-1(b)). (b) FTIR exhibiting the reduced N-H bonding by 1,2,4-triazole (Fig. 6-1(c)).

**Fig. 6-3.** Morphological and electrical characteristics of perovskite films. (a) SEM images of the 1,2,4-triazole-alloyed perovskite. (b) Film roughness and conductivity of 1,2,4-triazole-alloyed perovskite, as measured by AFM and 4-point probe. The 6%-alloyed film exhibits PbI$_2$ phase, leading to high roughness and conductivity.

**Fig. 6-4.** Roughness of perovskite films. Topology of bare and 1,2,4-triazole-alloyed perovskite films.

**Fig. 6-5.** Optical images of bare and 1,2,4-triazole-alloyed perovskite.

**Fig. 6-6.** Carrier and optoelectronic properties of perovskite films. (a) Carrier lifetime of 1,2,4-triazole-alloyed perovskite: TRPL, PL data, and bandgap determination by $(ahv)^2$ vs. $hv$. (b) Electronic structures of 1,2,4-triazole-alloyed perovskite by UPS: work function and VBM.

**Fig. 6-7.** Changes in the (a) bandgap and (b) VBM of 1,2,4-triazole-alloyed perovskite.

**Fig. 6-8.** Electronic-trap states of perovskite films. (a) Capacitance-frequency plot and (b) trap-distribution spectra of solar cells with the 1,2,4-triazole-
alloyed perovskite. (c) Schematic illustration for the band diagram and trap state in the device.

Fig. 6-9. Photovoltaic performance of perovskite solar cells. (a) J-V curves (scan rate: 10 mV s⁻¹), (b) steady-state current for 1000 s, and (c) EQE spectra for the bare and 1,2,4-triazole-alloyed perovskite solar cells. (d) TRPL spectra with the bare and 1,2,4-triazole-alloyed perovskite (FTO/SnO₂/perovskite/spiro-OMeTAD).

Fig. 6-10. Device reproducibility of bare and 1,2,4-triazole-alloyed perovskite.

Fig. 6-11. Device stability under 85°C/85% RH environment (encapsulated).
List of Tables

Chapter 1

Chapter 2
Table 2-1. Power conversion efficiencies of MAPbI₃ perovskite solar cells from the reactions 1, 2, 3, 4, and iso-propanol.
Table 2-2. Photovoltaic performance of MAPbI₃ perovskite solar cells using an ethanol or iso-propanol solution (as-fabricated cells and cells after 30 days).
Table 2-3. Precursor ratio of PbCl₂: MAPbCl₃ for the reactions 1, 2, 3, and 4.
Table 2-4. Solar cell performance from the reactions 1, 2, 3, and 4 (as-fabricated cells and cells after 30 days).

Chapter 3
Table 3-1. Optimization steps of PCE for the double-step deposition by tuning the conditions of sputter (up to 50 nm) and solution (up to 0.45 M).
Table 3-2. Calculated grain size of perovskite using Scherrer equation.
Table 3-3. Photovoltaic parameters of the perovskite solar cells from the highest efficiency device by more than 5 cells in each condition (with details in Tables 3-1 and Fig. 3-4).
Table 3-4. PCEs of MAPbI₃ perovskite solar cells from the sputtering, solution, and double-step deposition.
Chapter 4

Chapter 5

Table 5-1. Device performance vs. SnO$_2$ annealing temperature. Short-circuit current ($J_{sc}$), open-circuit voltage ($V_{oc}$), fill factor ($FF$), and power-conversion efficiency ($\eta$) of the champion cells (reverse direction). Full $J$-$V$ characteristics are shown in Fig. 5-3.

Table 5-2. Work function, valence band maximum, and bandgap of each SnO$_2$ layer. Fermi level of SnO$_2$ film is calculated from $E_F$ (= work function) = $h\nu$ - $E_{cutoff}$ with $h\nu = 21.22$ eV. Bandgap of SnO$_2$ has been estimated from the Tauc plot in Fig. 5-8(c).

Table 5-3. Electronic trap density and defect energy level $E_0$ (Fig. 5-9).

Chapter 6

Table 6-1. The highest and average values of the device performance. Photovoltaic performance of perovskite solar cells with 1,2,4-triazole alloyed
Chapter 1.

Overview of Perovskite Photovoltaics

1.1 Operation Mechanism of Solar Cells

The solar cell functions with the photovoltaic effect, converting light energy into charges to generate an electricity. This type of energy conversion is cost-effective and clean approach to support the energy consumption. The basic principle for solar energy conversion is shown in Fig. 1-1. The solar cell consists *n*-type and *p*-type material, which collect and transport the electrons and holes generated from a light absorbing material. Electrons and hole pair generates from the incident photon has a greater bandgap of the material. Simply, the incident light comes through the transparent conducting oxide (TCO), light absorbing material produces hole and electron pair to generate the electricity by the electric field existing at the *p*-*n* junction [1,2]. In order to generate hole and electron pair efficiently, bandgap of light-absorbing material should satisfy the solar spectrum as shown in Fig. 1-2. Therefore, the bandgap between 1.2~1.5 eV can be called as a proper material for photo-induced charge generating material [3-5].

The performance of solar cell is defined as power conversion efficiency (PCE), defining by the multiplication of short-circuit current (*J*<sub>sc</sub>), open-circuit voltage (*V*<sub>oc</sub>), and fill factor (FF). While the solar cell is in the operating situation, as shown in Fig. 1-1, the incident light or photons are
absorbed by light harvesting material, producing photo-exited electrons and holes, which will be utilize as current density. In order to obtain high $J_{sc}$, bandgap of light harvesting material must be small enough to absorb much of incident light. However, PCE isn’t the single component of $J_{sc}$, requiring $V_{oc}$ and fill factor (FF) to generalize the device performance. PCE is defined as $J_{sc} \times V_{oc} \times FF$, where the $V_{oc}$ can be determined by the quasi-fermi difference of material, requiring high and proper bandgap and band alignment. Therefore, bandgap should be optimized to exhibit the both high $V_{oc}$ and $J_{sc}$ (details are shown in Fig. 1-3) [6].

Performance of single-junction photovoltaic can be examined by the Shockley and Queisser limit, regarding on the one-sun efficiency by using the bandgap of light-absorbing material [2,7]. Throughout the extensive works, as shown in Fig. 1-4, different types of solar cell material are approaching its limit, requiring further strategy to compete against the energy market [2]. Therefore, the tandem structured device has introduced to overcome the limit, using the high bandgap and low bandgap material to boosts the limit of single-junction cell [8-10]. The structure of tandem solar cell can be separated into two different parts, two-terminal and four-terminal cells (Fig. 1-5), requiring may room to utilize the process and material for future uses [8]. Moreover, multi-junction solar cell can be designed to explore the potential of photovoltaics.
Fig. 1-1. Energy-band diagram of a silicon $p$-$n$ junction solar cell. From Ref. [1].
Fig. 1-2. Solar spectrum and the energy production of light-induced solar cells. From Ref. [3].
Fig. 1-3. $J$-$V$ characteristic and factors in solar cells. From Ref. [6].
Fig. 1-4. Plots for recorded solar cell efficiencies and S-Q limit. From Ref. [3].
Fig. 1-5. (a) 4-terminal, (b) 2-terminal, (c) four-terminal optical spectral splitting, and (d) four-terminal reflective tandem solar cells. From Ref. [8].
1.2 Application of Perovskite in Solar Cells

Perovskite can be formed in many different types, such as oxide-based or organometallic perovskite, and the organometallic perovskite can be utilized efficiently due to its suitable bandgap and physical properties [11-14]. Also the cost of perovskite is very cheap and the deposition can be easily done below 100°C, allowing the strong advantage in a market competition. General chemistry of organometallic perovskite consists ABX₃, where A is CH₃NH₃⁺ (MA), CN₂H₅⁺ (FA) or Cesium, B is Pb²⁺ or Sn²⁺, and X is I⁻ or Br⁻ (as shown in Fig. 1-6), and the property of material can be largely changed by the combination of A, B, and X [15,16]. In most of cases, many works utilized MAPbI₃ or FAPbI₃ framework to the solar cell due to the suitable property, but Br or Sn is often use as solute to stabilize or improve the device, which will be discussed in Chapter 1-5.

Application of organometallic perovskite is firstly demonstrated by Miyasaka group in 2009 with the 3.8% of PCE. Within 10 years of researches PCE is boosted to 24.2%, which is competitive against the commercialized Si-based solar cells [2,17-19]. Perovskite solar cells obtains transparent conducting oxide (TCO) / n-type layer / perovskite/ p-type layer / gold, and the early version of device used liquid based p-type electrolyte, leading extremely poor stability (as shown in Fig. 1-7), but the utilization of solid p-type and encapsulation techniques lead the improvement of solar cell stability [20,21]. Also, the different types of architecture (inverted structure) has also explored to widen the application of materials and processes [22]. Moreover the depositions of individual layers were widely studied
to obtain high PCE and stability [23].

The perovskite material obtains superior intrinsic properties such as high absorption coefficient and low defect density with the ambipolar charge transport property, leading the highly performable device as shown in Fig. 1-8 [24,25]. Moreover, the bandgap of perovskite can be tunable from 1.2 eV to 2.3 eV by substitution of different ion in perovskite chemistry [as presented in Fig. 1-9]. These facts are highly important because tunable bandgap allows the application of tandem solar cells and other displays, widening the study and application of perovskite [26].
Fig. 1-6. Schematic representation of the organometallic perovskite with species A, B and X. From Ref. [15].
Fig. 1-7. Band diagram of perovskite solar cells with the different device architectures and materials. From Ref. [22].
Fig. 1-8. Absorption coefficient and relation between Urbach energy of various solar cell materials. Charge mobility and defect of perovskite. From Ref. [25].
Fig. 1-9. Tunable bandgap of perovskite by halide exchange. From Ref. [26].
1.3 Deposition of Perovskite Photovoltaics

Fabrication of perovskite photovoltaics requires the deposition of $n$-type layer, perovskite, $p$-type layer, and gold on a TCO substrate. In general, deposition of $n$- or $p$-type material on a TCO goes first (depends on $n$-$i$-$p$ or $p$-$i$-$n$ structure, where $i$ indicates perovskite layer), then deposit perovskite on an $n$- or $p$-type layer next. After, deposit the remaining $n$- or $p$-type material on the perovskite layer. Lastly, deposit the counter electrode (gold) to finish up the solar cell fabrication. Majorly, vacuum and solution processed depositions were widely introduced to utilize the efficient layer (simple schematic shown in Fig. 1-10) [27]. To make a complete device, both vacuum and solution depositions are required, but the process cost should be considered.

Solution deposition regularly separates into precursors and nanoparticles. Precursor deposition is the deposition of reactant and add the thermal or external inputs to complete the reaction, then the creation of grain nucleation occur on a substrate as shown in Fig. 1-11 [28]. Precursor deposition is highly preferable to make a uniform and compact film, but the external input, such as heat or chemical can damage other layers such as TCO, $n$-, perovskite, or $p$-type layers [29]. Therefore, precursor deposition is generally preferable for the low temperature synthesis and the non-reactive substrate. On the other hand, nanoparticle deposition is quite direct. After synthesize the material, those material are dilute into the dispersive solvent, then deposit on a substrate to complete the film fabrication. Even though the temperature should applied to evaporate the
dispersive solvent, the temperature isn’t very high [30]. However, nanoparticle deposition is quite limited to make a high quality film. Nanoparticle deposition has to consider the size of nanoparticle and adhesion energy between the substrate and material during the deposition, and also the property of dispersive solvent because it can vary the quality of film. Therefore, solution based deposition should be carefully carried out to make a high quality film.

Vacuum deposition is theoretically the best option for the film deposition due to the clean and slow processes. Majorly, sputtering, evaporation, and atomic layer depositions (ALD) are the main depositions in the fabrication of perovskite photovoltaics [28-30]. Although atomic layer deposition is known for the fabrication of ideal deposition, the process and costs are slow and expensive. Also the temperature cannot go high, limiting the synthesis of metal oxides (those require high temperature to fabricate). On the other hand, sputter is suitable to deposit metal oxides by applying plasma energy, but the sputtering damage is too strong, diminishing the substrate [31]. Lastly, thermal evaporation suitable for the deposition of metal oxides or organometallic system but the uniformity of film is poor. Regardless on the advantages and disadvantage of vacuum depositions, the process cost is highly expensive when it was compared with cost of solution process, requiring alternative solution to reduce cost and improve the quality of film [29].
Fig. 1-10. (a) Vacuum, (b) and (c) solution process, and combination of vapor and solution depositions of perovskite film. From Ref. [27].
Fig. 1-11. Thermodynamic nucleation of precursor-processed perovskite (MAPbI$_3$). From Ref. [28].
1.4 Degradation Issues in Perovskite Solar Cells.

Perovskite photovoltaics established enormous PCE growth within 6 years, and settled as strong candidate as a next generation photovoltaics. However, the perovskite solar cell obtains major issue for the commercialization, which is the stability. While the solar cell is in the operating conditions, the device is exposed under an ambient and illuminating conditions. Ambient condition can be extreme, such as high temperature conditions or humid conditions, leading the damages of materials and solar cells. Also illumination produces latent heat, causing the additional problem in solar cell stability.

As discussed, perovskite solar cell consists $n$-type, perovskite, and $p$-type material (assume that TCO and Au are stable). Among the various degradation factors, humidity is directly related to the degradation of organometallic perovskite. Organometallic perovskite obtains organic site, such as FA and MA, and those ions form an oxygen bonding with the skeletal structure of metal halide. When the water atom attacks the organometallic perovskite, organic cation interacts with cation to ruin the structure of perovskite (as shown in Fig. 1-12) [32,33]. Moreover, organic site of organometallic perovskite reactive in aqueous solution, which causes the serious problem in solution manufacturing process.

Heat is also the main factor in the degradation of perovskite solar cells. Organometallic perovskite obtains organic compound and it is very volatile, which easily dissociate from the perovskite structure when the heat is induced (as shown in Fig. 1-13) [34,35]. Moreover, heat-induced degradation is also related to the
stability of \( p \)-type organics. Polymer or small organics were widely used as \( p \)-type material. Those organic compounds obtain low hole-mobility compared to the inorganic compound, requiring doping of metal with additives \([36,37]\). When the heat is induced, as shown in Fig 1-14, dopant and additives starting to evaporate and react with the perovskite layer, resulting in the destruction of the device.

Light is also the major issue in the degradation of perovskite solar cells. When the light comes in through the TCO, it react with metal oxide (majorly) or perovskite layer. Most of metal oxide has photocatalytic activity, making the oxygen radical inside of layer, and produced oxygen radical make a reaction with the organic site of perovskite to form a gaseous phase to damage the overall devices (shown in Fig. 1-15) \([38,39]\). Not only the issue of metal oxide layer, but also the perovskite itself has a problem with the light. When the device is exposed under the illuminating condition, gas evolution of organic halides and hydrogen halide starts to occur, leading the degradation of perovskite and solar cells, which shown in Fig. 1-16 \([40]\).

Although the perovskite had a significantly showed the potential as a next generation photovoltaics, management of surrounding attack should be handled for the future commercialization. There were many establishment has made to sustain long-term stability, yet the intrinsic property of organic part of perovskite and \( n \)- or \( p \)-type layer should be further investigated to compete against the other types of solar cells.
Fig. 1-12. (a-c) Water-induced degradation of perovskite layer, and (a,b,d) the passivation layer to block the water damage. From Ref. [32].
Fig. 1-13. Evolution of LBIC mapping of perovskite at the different temperature and relative humidity. From Ref. [35].
Fig. 1-14.  Degradation mechanism of metal doped Spiro-OMeTAD. From Ref. [36].
Fig. 1-15. Degradation mechanism of photocatalyzed metal oxide and perovskite.

From Ref. [38].
Fig. 1-16. Light-induced degradation of perovskite. From Ref. [40].
1.5 References


Chapter 2.

Solvent and Intermediate Phase as Boosters for the Perovskite Transformation and Solar Cell Performance

2.1. Introduction

The feasible challenges in solar cell commercialization are enhancement in power conversion efficiency (PCE) and cost reduction to support the world-wide electricity consumption [1–5]. Alternatively, organometallic perovskite solar cells were first demonstrated by Miyasaka’s group in 2009 with a PCE of 3.8% [6], and an enormous growth has been achieved over the last 6 years with the highest efficiency of 22.10% [7]. Perovskite \((\text{CH}_3\text{NH}_3\text{PbI}_3)\) solar cells are settled as the most attractive topic in photovoltaic research areas due to the low fabrication cost and high efficiencies, followed by inherent advantages of the perovskite material which include an appropriate and direct bandgap, small exciton binding energy, balanced ambipolar charge transport properties, etc. [8–12]. Furthermore, the synthesis of \(\text{CH}_3\text{NH}_3\text{PbI}_3\) (MAPbI\(_3\)) goes through a simple process, by mixing PbI\(_2\) and MAI precursors [6]. In 2012, the superior performance via MAPbI\(_3\) synthesis with PbCl\(_2\) and MAI precursors was introduced by Snaith’s group, and property analyses were carried out by many groups [13–16]. Since then, researchers widely studied the chlorine effect, and concluded that chlorine enhances the morphology of perovskite films [16–20]. Even though the chlorine effect is suggested by many research groups, understanding the mechanisms on the synthesis is still required to
be elucidated.

Architectural challenges are widely studied due to the ambipolar behavior \cite{21-23} of perovskites. Among them, the highest efficiency of 22.10\% \cite{7} has been achieved with mesoporous structure, and mesoporous layer allows the additional light trapping effect \cite{24,25}. In the mesoscopic structure, there are two major MAPbI$_3$ deposition methods. The one-step solution deposition generally uses a mixture solution of PbI$_2$ and MAI \cite{16}, and the sequential deposition is carried out by pre-depositing the PbI$_2$ film, followed by dipping it into an MAI-dissolved iso-propanol solution to form the MAPbI$_3$ film \cite{26}. Among them, the one-step solution deposition is highly beneficial in that this process is quite simple and time-saving. However, the sequential deposition is reported with a higher PCE than that of the one-step deposition \cite{27-29} due to the enhanced pore filling through the mesoporous TiO$_2$ (mp-TiO$_2$). Although the sequential deposition guarantees a high PCE, a comparative disadvantage in the sequential deposition is that it is a long-time process, since it goes through multiple steps to fabricate the perovskite film \cite{26}.

In this article, we have demonstrated a straightforward diffusion-controlled synthesis approach by replacing the conventional MAI-dissolved iso-propanol solution with a MAI-dissolved ethanol solution, which enhanced the crystallinity, boosted the perovskite transformation, and minimized impurities. Moreover, we have detected intermediate phases when the PbCl$_2$ precursor transforms into MAPbI$_3$, and engineered the MAPbI$_3$ deposition procedure by artificially mixing those intermediates as deposition precursors. This novel approach allowed superior surface morphology and crystallinity with enhanced conversion kinetics of MAPbI$_3$, yielding an initial PCE of 11.23\% and notable stability exhibiting 10.14\% PCE after 30 days under ambient conditions.
2.2. Experimental Section

*Perovskite Solar Cell Fabrication.* Fluorine-doped tin oxide substrate (FTO, TEC 8: Pilkington) was cleaned by sonication in Mucasol (Aldrich), ethanol (DEAJUNG), and DI water for 30 min sequentially. 50 nm of compact the TiO$_2$ blocking layer was deposited by spin-coating the mixture solution of 0.15 mM titanium diisopropoxide bis(acetylacetonate) (Aldrich) and 1-butanol (75.0 wt. % in isopropanol, Aldrich) in 2500 rpm for 20 s followed by heating at 125°C for 5 min in an air oven. The same step was repeated with 0.3 mM concentration and the substrate was annealed at 500°C for 30 min. After the TiO$_2$ blocking layer was ready, TiO$_2$ pastes (ENB Korea) with 20 nm-sized nanoparticles were mixed with terpineol (Aldrich) in 1:2 ratio, followed by spin-coating at 4000 rpm for 30 s, yielding a ~350 nm thickness of the mp-TiO$_2$ layer. For the perovskite synthesis, MAI was first synthesized by following literature method [26]. 1.5 M PbCl$_2$ (Aldrich) was diluted in dimethyl sulfoxide (DMSO, Aldrich), and then MACl (Aldrich) was added with different concentrations (0, 0.5, 1.0, and 1.5 M) to synthesize the reaction 1, 2, 3, and 4 precursors where the reaction 1, 2, and 3 precursors contain both MAPbCl$_3$ and PbCl$_2$ phases, whereas the reaction 4 precursor contains only MAPbCl$_3$ (MAPbCl$_3$ forms by 1:1 molar stoichiometric ratios of MACl and PbCl$_2$). After the preparation of precursor mixture solutions, the solution was preheated at 100°C and the substrate was preheated at 150°C, then the solution was spin-coated at 2000 rpm for 5 s, followed by 6000 rpm for 5 s. The film was annealed at 150°C for 30 min, and cooled down in an ambient condition. After the film was cooled down, it was dipped into 20 mg/mL of MAI in an anhydrous ethanol solution (Daejung) for 20 min under ambient conditions (25°C and 55% humidity) and annealed at 100°C for 30 min. The hole transport solution
was prepared by mixing 72.3 mg/mL of spiro-OMeTAD (Merck) in chlorobenzene (Aldrich) with 28.8 μL of tert-butylpyridine (Aldrich) and a 17.5 μL solution of 520 mg of lithium bis(trifluoromethylsulfonyl) imide salt (Aldrich) in 1mL acetonitrile (Aldrich) was spin-coated at 3000 rpm for 45 s. Finally, 100 nm thickness of an Au electrode was then thermally evaporated.

**Device Characterizations.** The morphologies of MAPbI₃ perovskite films were analyzed using scanning electron microscope (Normal-SEM, JSM-6360: Hitachi). The chlorine compositions and distribution were examined using energy-dispersive X-ray spectroscopy (EDS, ISIS-300: Oxford Instruments). The phases of the synthesized samples were characterized by X-ray diffraction (XRD, D8 Advance: Bruker). The photocurrent-voltage (J–V) curves of MAPbI₃ perovskite solar cells were obtained with a potentiostat (CHI 608C: CH Instrumental Inc.) under AM 1.5 illumination at 100 mW/cm² (K3000: McScience) with an active cell area of 0.09 cm². The field-emission scanning electron microscope (FE-SEM, Merlin-Compact: Carl Zeiss) was used to observe the plan and cross-sectional views. The absorption spectra of the MAPbI₃-deposited films were recorded on a UV-Vis spectrophotometer (Lambda 20: Perkin Elmer). Stability was measured every 5 days, and stored at 25°C with 55% of humidity under dark conditions.
2.3. Results and Discussion

2.3.1. Ethanol Conversion.  Sequential deposition is one of the most preferable methods for perovskite fabrication due to the high PCE. One major problem, however, is the long fabrication time by multiple fabrication steps [26]. To reduce the fabrication time in the sequential deposition process, boosting the formation kinetics of MAPbI$_3$ using MAI with PbCl$_2$ precursors is required. Therefore, a low viscous solvent and larger concentration of MAI are necessary for effective diffusion of MAI into the PbCl$_2$ layer. In general, conventional dipping solution uses 10mg/mL of MAI in iso-propanol [26], and a high concentration of MAI in solvent reduces both cuboid sizes and PCEs [30]. Thus, finding an alternative solvent is necessary for the viscosity and diffusion aspects. Figure 2-1 schematically illustrates the movements of ionized MAI into the PbCl$_2$ film with ethanol (20mg/mL) and iso-propanol (10mg/mL), where the conversion kinetics of PbCl$_2$ into MAPbI$_3$ for each solvent is quite different even with the optical images (Fig. 2-2, fast conversion kinetics with MAI/ethanol). The extent of the reaction was easily estimated by color changes ($E_g$ of MAPbI$_3$ $\approx$ 1.55 eV). However, less viscous methanol was not effective due to the dissolution of MAPbI$_3$ (Fig. 2-3) [26]. The fabricated perovskite film with the same concentration (20 mg/mL) for the iso-propanol solution results in rather small cuboid sizes (~80 nm) with a low PCE of 2.08% in the solar cell performance, as shown in Fig. 2-4. The cuboid size of MAPbI$_3$ with an ethanol solution is also distinguishable from that with iso-propanol, as shown in the scanning electron microscopy (SEM) (Figs. 2-5(a) and (b)). The PbCl$_2$-deposited film and cuboid-size distributions are plotted in Figs. 2-5(c), and the synthesized perovskite with twice-large cuboid sizes (~1180 nm) through an ethanol conversion is expected to produce higher carrier mobilities [31].
Fig. 2-1. Schematic illustration of the MAI in ethanol or iso-propanol diffusing into the PbCl$_2$-wetted mesoporous-TiO$_2$ (mp-TiO$_2$). The blocking-layer is coated on SnO$_2$:F (FTO).
Fig. 2-2. Time-dependent optical variation for the PbCl$_2$ films in the MAI/ethanol or MAI/iso-propanol solution.
Fig. 2-3. MAPb\textsubscript{I\textsubscript{3}} conversion using a methanol solvent: (a) SEM images for the MAPb\textsubscript{I\textsubscript{3}} film in different regions (20-min dipping sample), and (b) optical observations in every 5 min.
Fig. 2-4. SEM images of (a) MAPbI$_3$ and (b) $J$-$V$ curve from the 20-mg/mL MAI/iso-propanol solution.
Fig. 2-5. Solvent effects on MAPbI$_3$ using ethanol or isopropanol. (a) SEM images of MAPbI$_3$ using ethanol, (b) MAPbI$_3$ using iso-propanol, and (c) PbCl$_2$ on mp-TiO$_2$. The average cuboid size is shown for MAPbI$_3$ by ethanol or iso-propanol.
Figure 2-6 illustrates qualitative analysis of the perovskite formation with ethanol or iso-propanol. The energy disperse x-ray spectroscopy (EDS) was conducted to identify the chlorine concentration (Fig. 2-6(a)). MAPbI₃ converted from an ethanol solution contains lower Cl than that of iso-propanol-synthesized MAPbI₃ since unreacted PbCl₂ or partially-reacted MAPbCl₃ remains in the film. Still, ethanol-based MAPbI₃ shows some chlorine content, and we believe that this is caused by MACl which is a co-product during the MAPbI₃ synthesis [16–18]. Actually, there is a possibility that chlorine is doped in the perovskite structure (MAPbI₃ₓClₓ) as reported by several groups [14–16]. However, the small quantity of chlorine in the perovskite structure is difficult to be evaluated, and the remaining chlorine may form other products [17,19]. Cross-sectional SEM image of MAPbI₃ perovskite solar cell by ethanol exhibits uniform film structures, as shown in Fig. 2-6(b). For further understanding of impurities, X-ray diffraction (XRD) scans were compared, and an ethanol-based MAPbI₃ shows clear (110), (220) and (330) peaks (Fig. 2-6(c)). On the contrary, the conversion with iso-propanol produced impurity peaks of PbI₂ and MAPbCl₃ (Fig. 2-6(c)), indicating incomplete reaction. To explain the effect of ethanol on the crystallinity, we have additionally confirmed that the longer dipping time increases the crystallinity of MAPbI₃ (Fig. 2-7) even when the reaction was completed. Together with the optical observation in Fig. 2-2, it can be said that MAI/ethanol-converted MAPbI₃ completes the reaction faster with better crystallinity, compared to that of iso-propanol for the same dipping time. Furthermore, the light absorption from the synthesized perovskite is clearly different between ethanol and iso-propanol (Fig. 2-6(d)). The enhanced absorption at approximately 800 nm by ethanol is due to the superior purity of MAPbI₃ (Eg ≈ 1.55
eV), while partially-reacted MAPbI$_3$ by iso-propanol contains high-bandgap impurities, such as PbI$_2$ ($E_g \approx 2.36$ eV) [32] and MAPbCl$_3$ ($E_g \approx 3.17$ eV) [33]. Therefore, the overall PCE is greatly improved from 5.86% to 9.51% (Fig. 2-6(e)) with much better stability (Fig. 2-6(f)), and both methods performed high reproducibility (Fig. 2-8 and Table 2-1). After 30 days, the PCE decreased from 9.51% to 8.53% and 5.86% to 3.75%, respectively, for the ethanol and iso-propanol solution (Table 2-2). The improved crystallinity and enlarged grain of MAPbI$_3$ by ethanol surely prevents possible air penetration through various grain boundaries, leading to stability enhancement. The half-lifetime of the MAPbI$_3$ perovskite solar cell (degradation details in Fig. 2-9) was estimated to be ~150 and ~40 days, respectively, for ethanol and iso-propanol. To identify the reaction mechanisms, intermediate phases during the perovskite formation were investigated by the concentration variations of MAI in ethanol. With a low concentration of MAI/ethanol (Fig. 2-10(a)), PbCl$_2$ partially reacts into PbI$_2$ (5mg/mL). The chlorine in PbCl$_2$ ion-exchanges with iodine in MAI to form PbI$_2$, and the dissociated MA$^+$ and Cl$^-$ from outer PbCl$_2$ intercalate into the inner PbCl$_2$ layer, transforming to the MAPbCl$_3$ phase (15mg/mL of MAI/ethanol). The intermediate PbI$_2$ reacts with MAI directly to form MAPbI$_3$ by intercalating MAI in the layered PbI$_2$, while MAPbCl$_3$ will ion-exchange with I$^-$ and reconstructs to the final MAPbI$_3$, as schemed in Fig. 2-10(b) (20mg/mL of MAI/ethanol). The whole reaction occurs through the following steps:

\[
2 \text{PbCl}_2 + 2 \text{MAI} \rightarrow \text{PbI}_2 + \text{PbCl}_2 + \text{MACl} \quad \text{(step 1)}
\]

\[
\text{PbI}_2 + \text{MAI} \rightarrow \text{MAPbI}_3 \quad \text{(step 2)}
\]

\[
\text{PbCl}_2 + 2 \text{MACl} \rightarrow \text{MAPbCl}_3 + \text{MACl} \quad \text{(step 3)}
\]
MAPbCl₃ + MACl + 3 MAI → MAPbI₃ + 4 MACl (step 4)

PbCl₂ + 3 MAI → MAPbI₃ + 2 MACl (Total Reaction)

The PbI₂ phase converts into MAPbI₃ earlier than the formation of MAPbCl₃, as shown by the X-ray diffraction of MAPbI₃ vs. MAPbCl₃ phases for MAI concentrations of 10 and 15mg/mL (Fig. 2-10(a)). We have also compared the perovskite formation from MAPbCl₃ (MAPbCl₃ + 3 MAI → MAPbI₃ + 3 MACl) with PbI₂ (PbI₂ + MAI → MAPbI₃) (respectively, in the middle and right of Fig. 2-10(a)), and found that both have resulted in no intermediate phases. Synthesizing fully-converted MAPbI₃ from PbCl₂ requires both intercalation and reconstruction steps, while the idea of reconstruction from MAPbCl₃ to MAPbI₃ was investigated in the previous report [34]. Therefore, we intuitively conclude that the recrystallization of intermediates both inside and on top of the mp-TiO₂ film can enhance the coverage morphology, nanostructures, and crystallinity [16–18] of MAPbI₃ by multiple crystal-alignment steps. Moreover, ethanol conversion increases the kinetics of the reaction steps, and produces improved MAPbI₃ film, compared to the conversion with iso-propanol.
Fig. 2-6. The dependence of MAPbI$_3$ perovskite solar cells using the MAI in an ethanol or iso-propanol solution. (a) EDS mapping for iodine and chlorine in the synthesized MAPbI$_3$ with an ethanol (top) or isopropanol (bottom) solution. (b) Cross-sectional SEM image of a MAPbI$_3$ perovskite solar cell from the MAI/ethanol solution. (c) X-ray diffraction of MAPbI$_3$. (d) Absorption spectra for the synthesized MAPbI$_3$. (e) $J-V$ characteristics of the MAPbI$_3$ perovskite solar cells. (f) Degradation of solar cells synthesized by ethanol or isopropanol for the as-fabricated cells and cells after 30 days.
Fig. 2-7. X-ray diffraction from various MAI/ethanol dipping times on the PbCl$_2$ film.
Fig. 2-8. Device reproducibility of MAPbI$_3$ perovskite solar cells from the reactions 1, 2, 3, 4, and iso-propanol.
Table 2-1. Power conversion efficiencies of MAPbI$_3$ perovskite solar cells from the reactions 1, 2, 3, 4, and iso-propanol.

<table>
<thead>
<tr>
<th>Device</th>
<th>Iso-propanol</th>
<th>RXN 1</th>
<th>RXN 2</th>
<th>RXN 3</th>
<th>RXN 4</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>5.89%</td>
<td>8.87%</td>
<td>9.95%</td>
<td>6.95%</td>
<td>4.40%</td>
</tr>
<tr>
<td>2</td>
<td>5.87%</td>
<td>9.51%</td>
<td>11.00%</td>
<td>7.32%</td>
<td>4.03%</td>
</tr>
<tr>
<td>3</td>
<td>5.53%</td>
<td>9.43%</td>
<td>10.12%</td>
<td>7.31%</td>
<td>4.16%</td>
</tr>
<tr>
<td>4</td>
<td>5.84%</td>
<td>8.07%</td>
<td>11.19%</td>
<td>6.29%</td>
<td>3.76%</td>
</tr>
<tr>
<td>5</td>
<td>5.91%</td>
<td>8.76%</td>
<td>10.10%</td>
<td>6.87%</td>
<td>4.23%</td>
</tr>
<tr>
<td>6</td>
<td>5.31%</td>
<td>8.50%</td>
<td>10.10%</td>
<td>6.94%</td>
<td>4.24%</td>
</tr>
<tr>
<td>7</td>
<td>5.23%</td>
<td>8.55%</td>
<td>11.24%</td>
<td>6.44%</td>
<td>3.80%</td>
</tr>
<tr>
<td>8</td>
<td>5.15%</td>
<td>9.09%</td>
<td>10.00%</td>
<td>6.51%</td>
<td>3.83%</td>
</tr>
<tr>
<td>9</td>
<td>6.30%</td>
<td>8.55%</td>
<td>12.30%</td>
<td>6.67%</td>
<td>3.62%</td>
</tr>
<tr>
<td>10</td>
<td>5.86%</td>
<td>9.09%</td>
<td>11.80%</td>
<td>7.29%</td>
<td>4.58%</td>
</tr>
</tbody>
</table>
Table 2-2. Photovoltaic performance of MAPbI$_3$ perovskite solar cells using an ethanol or iso-propanol solution (as-fabricated cells and cells after 30 days).

<table>
<thead>
<tr>
<th>Reaction Condition</th>
<th>$V_{oc}$ (V)</th>
<th>$J_{sc}$ (mA/cm$^2$)</th>
<th>$FF$</th>
<th>$\eta$ (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Initial</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Ethanol</td>
<td>0.87</td>
<td>17.3</td>
<td>0.63</td>
<td>9.51</td>
</tr>
<tr>
<td>Iso-propanol</td>
<td>0.83</td>
<td>14.4</td>
<td>0.49</td>
<td>5.86</td>
</tr>
<tr>
<td>30 Days</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Ethanol</td>
<td>0.84</td>
<td>16.4</td>
<td>0.63</td>
<td>8.53</td>
</tr>
<tr>
<td>Iso-propanol</td>
<td>0.79</td>
<td>10.1</td>
<td>0.47</td>
<td>3.75</td>
</tr>
</tbody>
</table>
Stability of MAPbI$_3$ perovskite solar cells from the reactions 1, 2, 3, and 4 for 30 days. The corresponding data by iso-propanol (RXN 1) are also shown.
Fig. 2-10. Reaction intermediates and mechanism analysis by X-ray diffraction measurements. (a) Reaction 1 (left), reaction 4 (middle), and PbI$_2$ precursor (right) with various concentrations of MAI in an ethanol solution. (b) Mechanisms of reaction 1 (PbCl$_2$ + 3 MAI → MAPbI$_3$ + 2 MACl). The MAI and ethanol diffuse into the outer PbCl$_2$ layer, which converts PbCl$_2$ into PbI$_2$ and MACl. Additional MAI from the solution converts the synthesized outer PbI$_2$ into MAPbI$_3$, and MACl reacts with the inner PbCl$_2$ transforming into MAPbCl$_3$. The synthesized MAPbCl$_3$ ion-exchanges with I$^-$ for the full MAPbI$_3$ and MACl to complete the reaction.
2.3.1. Reaction Mechanism Engineering. To understand the phase-formation paths of MAPbI₃ from PbCl₂, we came up with an idea to further optimize MAPbI₃ by utilizing the identified intermediate phases. While the direct conversion of MAPbCl₃ to MAPbI₃ can drastically reduce the reaction time, the repetition of crystallization from PbCl₂ to MAPbI₃ will enhance the surface morphology. Even though PbI₂ appears during the transformation of the PbCl₂ precursor to MAPbI₃, and increases the reaction kinetics, the MAPbCl₃ precursor is more reactive than the PbI₂ precursor to synthesize MAPbI₃ (middle and right graphs in Fig. 2-10(a)) where the MAPbCl₃ precursor is likely to transform with lower MAI concentration than that of the PbI₂ precursor. Also, the chlorine-based precursor should be preferred considering the positive effects of chlorine on the MAPbI₃ perovskite solar cells [16–20]. Therefore, a straightforward direction is rendered by mixing PbCl₂ and MAPbCl₃ in several different ratios of 3:0 (reaction 1), 2:1 (reaction 2), 1:2 (reaction 3), and 0:3 (reaction 4), to optimize the reaction time with smooth surface morphology (Table 2-3 and Fig. 2-11).

As expected, we observed the morphology changes by synthesizing MAPbI₃ films from precursors with different ratios of PbCl₂ and MAPbCl₃ through SEM, as shown in Fig. 2-12(a). Perovskite films synthesized by reaction 2 exhibits clearly improved coverage with ~2320-nm-sized cuboids. Furthermore, addition of MAPbCl₃ (reaction 3 and 4) deteriorates the coverage, but increases the cuboid size. When a larger amount of the MAPbCl₃ precursor is added through reactions, the crystallinity of MAPbI₃ is enhanced significantly, as shown by XRD (Figs. 2-12
(b) and (c)). The enhanced crystallinity can be explained by the extent of reaction, and the facilely-transformed perovskite is likely to have high crystallinity even with the same dipping time (Fig. 2-7). These observations are also consistent with the optical variations during the MAPbI₃ formation (Fig. 2-13). It should be noted that the coverages for the reactions 1, 2, 3, and 4 are different. However, conversions at ~10 s are distinct between reactions 1 (PbCl₂ precursor) and 4 (MAPbCl₃ precursor). The light absorption in Figs. 2-12(d) indicates that the absorption is more influenced by the coverage rather than the crystallinity and cuboid size of MAPbI₃. The maximum coverage in reaction 2 reached the highest absorption, and the minimum coverage with reaction 4 yielded the lowest absorption. As a material perspective, MAPbI₃ synthesis by reaction 4 is supposed to show excellent properties due to the high crystallinity and cuboid sizes, as plotted in Fig. 2-14(a). Moreover, EDS was additionally measured to identify the comparative chlorine contents with iodine, which is plotted in Fig. 2-14(b) for each reaction, indicating that reaction 1 obtained the highest, and reaction 4 occupied the lowest concentration of chlorine. This chlorine tendency suggests that a co-product of MACl is minimized through the addition of MAPbCl₃ (It should be noted that the EDS technique may not reflect the accurate chlorine concentration due to the coverage difference of each reaction.). It is possible that the detected chlorine through EDS is from the MACl phase or other products [16–18]. Moreover, excessive chlorine may lead to impurities, and deteriorate the device performance. Therefore, high crystallinity and low impurity of MAPbI₃ are highly beneficial in the carrier mobilities, but recombination of
carriers arising from poor coverage [31] is another factor that we should be aware of.

To understand the effects of crystallinity and coverage on the photovoltaic performance and stability, $J-V$ curves are measured for 30 days under ambient conditions (Fig. 2-9, and Table 2-4). In Fig. 2-14(c), $J-V$ curves were shown for the performance of the solar cells from each reaction, and the highly covered perovskite film from reaction 2 achieved the highest PCE of 11.23%. The lowest PCE of 4.03% was obtained by reaction 4, and these results indicate that the initial PCE is highly dependent on the perovskite coverage, which plays crucial roles in the carrier recombination. In contrast, MAPbI$_3$ synthesized by reaction 4 was distinctively stable after 30 days. The stability is well correlated with the crystallinity and grain size, apparent from the normalized PCE in Fig. 2-14(d), confirming the reduced decomposition behavior from the low-defect perovskite. All of the solar cells with different experimental conditions performed high reproducibility (Fig. 2-8 and Table 2-1). From the reactions 1, 2, 3, and 4, the half-lifetimes of MAPbI$_3$ perovskite solar cells (degradation details in Supplementary Fig. 2-9) are estimated to be ~150, ~160, ~270, and ~300 days.
Table 2-3. Precursor ratio of PbCl$_2$: MAPbCl$_3$ for the reactions 1, 2, 3, and 4.

<table>
<thead>
<tr>
<th>Reaction Mechanism</th>
<th>Precursor Ratio (PbCl$_2$: MAPbCl$_3$)</th>
</tr>
</thead>
<tbody>
<tr>
<td>RXN 1</td>
<td>PbCl$_2$ + 3 MAI $\rightarrow$ MAPbI$_3$ + 2 MACl</td>
</tr>
<tr>
<td>RXN 2</td>
<td>2 PbCl$_2$ + MAPbCl$_3$ + 9 MAI $\rightarrow$ 3 MAPbI$_3$ + 7 MACl</td>
</tr>
<tr>
<td>RXN 3</td>
<td>PbCl$_2$ + 2 MAPbCl$_3$ + 9 MAI $\rightarrow$ 3 MAPbI$_3$ + 8 MACl</td>
</tr>
<tr>
<td>RXN 4</td>
<td>MAPbCl$_3$ + 3 MAI $\rightarrow$ MAPbI$_3$ + 3 MACl</td>
</tr>
</tbody>
</table>
Fig. 2-11. Schematic illustration of the experimental procedure. Various ratios of PbCl$_2$: MAPbCl$_3$ were initially deposited on the substrate, and then the MAI-dissolved ethanol solution was utilized to synthesize MAPbI$_3$. 
Fig. 2-12. The film quality dependence of MAPbI₃ for the reactions 1, 2, 3, and 4. (a) SEM images of the precursor and MAPbI₃, (b,c) X-ray diffraction for the precursor and MAPbI₃, and (d) absorption spectra of MAPbI₃ by reactions 1, 2, 3, and 4.
Fig. 2-14. Time-dependent optical variation for the reactions 1, 2, 3, and 4 in a MAI/ethanol solution.
<table>
<thead>
<tr>
<th>Reaction Conditions</th>
<th>$V_{oc}$ (V)</th>
<th>$J_{sc}$ (mA cm$^{-2}$)</th>
<th>FF</th>
<th>$\eta$ (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Initial</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>RXN 1</td>
<td>0.87</td>
<td>17.3</td>
<td>0.63</td>
<td>9.51</td>
</tr>
<tr>
<td>RXN 2</td>
<td>0.90</td>
<td>19.8</td>
<td>0.63</td>
<td>11.23</td>
</tr>
<tr>
<td>RXN 3</td>
<td>0.76</td>
<td>16.3</td>
<td>0.56</td>
<td>6.94</td>
</tr>
<tr>
<td>RXN 4</td>
<td>0.61</td>
<td>11.7</td>
<td>0.57</td>
<td>4.03</td>
</tr>
<tr>
<td>30 Days</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>RXN 1</td>
<td>0.84</td>
<td>16.4</td>
<td>0.62</td>
<td>8.53</td>
</tr>
<tr>
<td>RXN 2</td>
<td>0.89</td>
<td>17.8</td>
<td>0.64</td>
<td>10.14</td>
</tr>
<tr>
<td>RXN 3</td>
<td>0.73</td>
<td>15.2</td>
<td>0.59</td>
<td>6.55</td>
</tr>
<tr>
<td>RXN 4</td>
<td>0.61</td>
<td>11.7</td>
<td>0.52</td>
<td>3.83</td>
</tr>
</tbody>
</table>

Table 2-4. Solar cell performance from the reactions 1, 2, 3, and 4 (as-fabricated cells and cells after 30 days).
2.4. Conclusions

Fast conversion can have positive influences on the device performance and stability by producing highly-crystalline MAPbI$_3$ perovskite. Therefore, we have controlled the diffusion reaction of MAI and PbCl$_2$ with ethanol to boost the perovskite transformations, leading to phase-pure and highly-crystalline perovskite films. Since PbCl$_2$ goes through several intermediate phases during the formation of MAPbI$_3$, we utilized the intermediates by mixing them with a conventional PbCl$_2$ precursor to boost the conversion kinetics and performance of the resulting solar cell. Thereby, the optimized crystallinity and coverage yielded a PCE of 11.23% with PbCl$_2$: MAPbCl$_3$ = 2:1 (reaction 2). Although the precursor with 100% MAPbCl$_3$ (reaction 4) resulted in the fastest transformations of MAPbI$_3$ and the most stable solar cell performance, poor coverage lowered the PCE of the device. Therefore, compact coverage of the perovskite with super-sized cuboids expects to achieve further enhanced performance and stability of the MAPbI$_3$ perovskite solar cell. At this point, investigation of hysteresis still remains as a future work.
2.5. References


30th March, 2016).


83

Chapter 2


Chapter 3.

Synergetic Effect of Double-Step Blocking Layer for the Perovskite Solar Cell

3.1. Introduction

The organometallic CH$_3$NH$_3$PbI$_3$ (MAPbI$_3$) perovskite solar cells have received enormous attention as next generation photovoltaics due to the potential strength of high power conversion efficiencies (PCEs) and low fabrication cost [1–13]. The perovskite semiconductor satisfies appropriate and direct bandgap, small exciton binding energy, and balanced ambipolar charge transport properties [14–18]. Even though the PCE of perovskite solar cell has reached 22.10%, it still has a potential to enhance the performance up to the theoretical limit of 31.40% [19,20].

The role of blocking layer in the perovskite solar cell is crucial because it prevents the recombination of electrons from a transparent conducting oxide (TCO) to the perovskite layer, impacting hugely on the performance of solar cells [21–24]. Among various deposition methods, spray-pyrolysis and solution spin-coating are well known techniques in the field of perovskite solar cells due to their low cost and easiness of process [25–29]. In 2014, a compact layer using atomic layer deposition (ALD) was introduced with high PCE [30–32]. Nevertheless, ALD is inadequate to the large scale production due to its slow deposition rate and reaction.
sensitivity [33]. On the other hand, the deposition is extensively utilized in industry owing to the fast deposition rate and compactness of the film and was also introduced with solar cell fabrication [2,6,10,34,35]. Even though the sputtering deposition can construct a compact layer, TiO$_2$ by sputtering yields some porous structure that allows the carrier recombination, and thereby, post-treatment or further improvement is still required [35].

Herein, we demonstrate the double-step deposition method, through a combination of sputter and solution to construct a vastly compact blocking layer. Compact TiO$_2$ layer was first deposited by sputtering, and any remaining pores were facilely post-treated through the solution process. As a result, the transmittance and uniformity of the blocking layer were largely improved. Consequently, the utilization of double-step deposition provided a favorable environment for the perovskite growth, leading to the enhancement of crystallinity and morphology of the perovskite layers. Conclusively, this straightforward double-step deposition improved the quality of the perovskite solar cell, reducing the recombination rate and thereby yielding high solar-cell efficiency.
3.2. Experimental Section

Synthesis of TiO$_2$ blocking layer. Fluorine-doped tin oxide substrate (FTO, TEC 8: Pilkington) was cleaned by sonication in Mucasol (Aldrich), ethanol (Daejung), and de-ionized (DI) water for 30 min sequentially. The sputter-based TiO$_2$ blocking layer was fabricated by sputtering system. With the TiO$_2$ target (anatase, 99.99%, RND Korea), the deposition was performed at room temperature (RT) under an Ar atmosphere with an operating pressure of and rf power of 100 W for 100 min. The solution-based TiO$_2$ blocking layer was deposited by spin-coating the mixture solution of 0.15 M titanium diisopropoxide bis(acetylacetonate) (75.0 wt. % in isopropanol, Aldrich) and 1-butanol (Aldrich) at 2500 rpm for 20 s, followed by heating at 125°C for 5 min in an air oven. For the double-step deposition, sputter deposition was first performed for 60 min. Then, the 0.15 M mixture solution was spin-coated. The substrates with three different conditions were annealed at 500°C for 30 min.

Solar-cell fabrication. After the TiO$_2$ blocking-layer deposition, TiO$_2$ pastes (ENB Korea) with 20 nm nanoparticles were mixed with terpineol (Aldrich), followed by spin-coating at 4000 rpm for 30 s, yielding a 350 nm thickness of mesoporous TiO$_2$ (mp-TiO$_2$) layer. For the perovskite synthesis, the solution of 1.5 M PbCl$_2$ (Aldrich) diluted in dimethyl sulfoxide (DMSO, Aldrich) was preheated at 100°C, and spin-coated at 2000 rpm for 5 s, followed by 6000 rpm for 5 s on the preheated substrate at 150°C. The film was annealed at 150°C for 5 min, cooled down in an ambient condition (25°C and 55% humidity), and dipped into of synthesized CH$_3$NH$_3$I (MAI) in an anhydrous ethanol solution (Daejung) for 20 min, followed by annealing at
The hole transport material (HTM) was prepared by mixing 72.3 mg/mL of spiro-OMeTAD (Merck) in chlorobenzene (Aldrich), with 28.8 uL of (Aldrich) and a 17.5 uL solution of 520 mg of lithium bis(trifluoromethylsulfonyl) imide salt (Aldrich) in 1 mL acetonitrile (Aldrich), and was at 3000 rpm for 45 s. Finally, 100-nm-thick Au electrode was thermally evaporated.

**Device characterization.** The field-emission scanning electron microscope (FESEM; Merlin-Compact: Carl Zeiss) was used to observe the morphologies of blocking layer and MAPbI$_3$. The phases of the synthesized samples were characterized by X-ray diffraction (XRD; D8 Advance: Bruker). The photocurrent-voltage ($J–V$) curves of MAPbI$_3$ perovskite solar cells were obtained with a potentiostat (CHI 608C; CH Instrumental Inc.) under AM 1.5 at 100 mW/cm$^2$ (K3000; McScience) with an active cell area of 0.09 cm$^2$ and 10 V/s of scan rate. The transmittance spectra of the MAPbI$_3$ and blocking layers were recorded on a UV-vis spectrophotometer (Lambda 20; Perkin Elmer), and the electrochemical impedance spectra (EIS) were measured by a potentiostat with 20 mV sinusoidal perturbation and frequencies ranging from $10^{-1}$ to $10^5$ Hz. The topography data were obtained utilizing atomic-force microscopy (AFM; XE-70: Park System). An external quantum efficiency (EQE) measurement system (K3100; McScience, Korea) was used to obtain the EQE spectra.
3.3. Results and Discussion

To resolve the carrier recombination problem, a highly compact blocking-layer is required. While sputter deposition is one option with energetic sputtered atoms (5 eV), it still yields a porous structure that allows some recombination [35,37]. Therefore, we have deposited TiO₂ by sputtering first and then filled up any porous channels with solution-based precursors (with the optimization step as illustrated in Table 3-1 and Fig. 3-1, supplementary material). Schematics and (Fig. 3-2) represent the expected nanostructures of the blocking layer, and the arrow size indicates the level of carrier recombination, which would be controlled by the compactness of blocking layer. However, band alignment of all three conditions stays the same, because sputter and solution both yield anatase-phase TiO₂ [38,39]. Previous studies identified that sputter-deposited blocking layer performs better than that of the solution owing to the high compactness of the film [34]. However, the cross-sectional and plan views of the sputter deposition present inevitable pinholes that can seriously degrade the cell performance (Fig. 3-3(a)). In addition, the cross-sectional image of solution deposition provides non-uniform and porous structure, with clear pinholes in plan-view (Fig. 3-3(b)). In contrast, the double-step deposition has more dense morphology with high uniformity (Fig. 3-3(c)). For the rational comparison, the
blocking layers were deposited with an equal thickness of for each deposition, which is an optimum value for sputtered TiO$_2$ as shown in Fig. 3-4. Transmittance was measured in Fig. 3-5. Both solution and sputter-deposited TiO$_2$ blocking layer obstructed a bit less than 60% of light at 300 nm region, where the transmission onset begins at 390 nm (bandgap of TiO$_2$ = 3.2 eV) [40]. On the other hand, the double-step deposition blocked approximately 90% of light, which indicates lower transmittance than that of sputter- or solution-based blocking layer. Also, solution-deposited TiO$_2$ shows some humps between 350 and 600 nm regions. These humps indicate the high roughness of film that addresses the poor quality of the film (also shown in Fig. 3-3(b)) [41]. Despite the compactness of the blocking layer, lower transmittance of double-step deposition can hinder the generation of photo-induced electrons under 350 nm region (bandgap region of TiO$_2$). However, the extent of solar irradiation is comparatively low under 350 nm, whereas the visible region has high solar irradiation [42]. Therefore, the detrimental effect of low wavelength region is negligible, and the compactness of TiO$_2$ is highly important with the satisfaction of good layer construction, efficient charge transport, and less possibility of carrier recombination in the solar cell.
<table>
<thead>
<tr>
<th></th>
<th>0 M</th>
<th>0.10 M</th>
<th>0.15 M</th>
<th>0.30 M</th>
<th>0.45 M</th>
</tr>
</thead>
<tbody>
<tr>
<td>0 nm</td>
<td>x</td>
<td>x</td>
<td>3.60%</td>
<td>x</td>
<td>x</td>
</tr>
<tr>
<td>10 nm</td>
<td>x</td>
<td>x</td>
<td>5.15%</td>
<td>4.08%</td>
<td>x</td>
</tr>
<tr>
<td>20 nm</td>
<td>x</td>
<td>x</td>
<td>6.10%</td>
<td>5.80%</td>
<td>x</td>
</tr>
<tr>
<td>30 nm</td>
<td>4.28%</td>
<td>6.88%</td>
<td>12.31%</td>
<td>7.57%</td>
<td>6.27%</td>
</tr>
<tr>
<td>40 nm</td>
<td>x</td>
<td>x</td>
<td>6.86%</td>
<td>5.57%</td>
<td>4.84%</td>
</tr>
<tr>
<td>50 nm</td>
<td>x</td>
<td>x</td>
<td>6.54%</td>
<td>5.16%</td>
<td>4.45%</td>
</tr>
</tbody>
</table>

Table 3-1. Optimization steps of PCE for the double-step deposition by tuning the conditions of sputter (up to 50 nm) and solution (up to 0.45 M).
Fig. 3-1. Concentration control of a TiO$_2$ solution on the sputter-deposited TiO$_2$ to optimize the performance of perovskite solar cell (with hole-transporting material).
Fig. 3-2. Schematics and energy diagrams of the solar cells with various TiO$_2$ blocking layers deposited by sputter, solution, or double-step method. Red arrows indicate the recombination phenomena of carriers.
Fig. 3-3. Cross-sectional and plan-view SEM images of blocking-layer TiO$_2$ by (a) sputter, (b) solution, and (c) double-step deposition.
Fig. 3-4. Performance optimization of the perovskite solar cell by varying the thickness of sputter-deposited TiO$_2$. 
Fig. 3-5. Transmittance from the differently deposited blocking layers (before the solar-cell fabrication).
On top of the fabricated blocking layer, mp-TiO$_2$ layer was additionally deposited to transport electrons more efficiently from the perovskite [23,43]. The SEM images in Fig. 3-6 for each deposition present distinctive perovskite morphologies. As shown in Figs. 3-6(a) and (c), aggregated perovskite grains are constructed by stacking both on a side and top. Therefore, the sputter processed blocking layer yielding a rough semiconductor morphology (Fig. 3-6(a)), whereas solution deposition produced a smooth layer with few pinholes (Fig. 3-6(b)). With the double-step deposition, perovskite was more densely covered (Fig. 3-6(c)). To further confirm the roughness of film, atomic-force microscopy (AFM) is additionally conducted (Fig. 3-7), which revealed higher RMS roughness for the perovskite on the sputter-processed TiO$_2$ than others, and lowest RMS roughness in solution. Therefore, higher number of aggregated perovskite increased the RMS roughness due to the different grain-growth environment. As the double-step strategy exhibited distinctive morphologies for both blocking and perovskite layers, additional analyses were performed to advocate the synergetic effect of double-step deposition. Figure 3-8(a) illustrates X-ray diffraction of the perovskite with each blocking-layer method. The double-step deposition exhibited the highest crystallinity compared with either sputter or solution deposition (grain sizes of each condition is calculated in Table 3-2), and these phenomena can be addressed from the previous report that perovskite does not crystallize sufficiently on the FTO substrate [43-45]. Therefore, highly compact blocking TiO$_2$ layer by the double-step deposition can be a useful method to produce excellent quality of crystallized perovskite. Furthermore, the sputtering deposition resulted in the lowest transmittance, and the second lowest for the double-step (Fig. 3-8(b)). Due to the
aggregation phenomena of sputter and double-step shown in Fig. 3-6, perovskite layer by sputter deposition transmitted less light compared to that of double-step. However, since device performance does not depend solely on the light transmittance of photon absorber, further investigation of other layers and devices should be elucidated. To understand the effect of blocking layer in a solar cell performance, $J-V$ curve was measured, and the highest PCE of 12.31% was achieved with the double-step deposition (Fig. 3-8(c), Table 3-3), and reproducibility is checked as shown in Table 3-4 and Fig. 3-9 (supplementary material). As shown in Fig. 3-8(d), EQE spectra of solar cells exhibited the highest value for the double-step deposition, especially at long wavelength region. Even though the light absorption in the sputter-based perovskite solar cell was higher than that in the double-step deposition, compactness of blocking layer and well-crystallized perovskite in the double-step based perovskite solar cell collects charge carriers better than that of sputter or solution. For the further investigation of devices, impedance spectroscopy was carried out under dark condition at various voltages (Fig. 3-10). Tendency of semi-circle at each voltage elucidates that the double-step has the highest recombination resistance, whereas solution reached the lowest (with the calculation values in Table 3-5). Conclusively, recombination resistance of double-step can be explained by the dense morphology of blocking and perovskite layer, and the solution process yielded the lowest resistance owing to its porous and pinhole structure of the blocking layer, which critically causes the carrier recombination. Additional Nyquist-plot data with the fitting profile are shown in Figs. 3-11 and 12.
Fig. 3-6. Schematics with top-view SEM images of MAPbI₃/mp-TiO₂/BL-TiO₂/FTO: (a) sputter, (b) solution, and (c) double-step deposition.
Fig. 3-7. Topography maps and RMS values of the perovskite films obtained from atomic-force microscopy (AFM).
Fig. 3-8. Crystallinity and optoelectrical properties of MAPbI$_3$ devices on various blocking layers: (a) X-ray diffraction, (b) transmittance of MAPbI$_3$ films, (c) $J$-$V$ curves (a scan rate of 10 V/s), and (d) EQE spectra of the perovskite solar cells.
Table 3-2. Calculated grain size of perovskite using Scherrer equation.

<table>
<thead>
<tr>
<th>Grain size (nm)</th>
<th>Sputter</th>
<th>Solution</th>
<th>Double-step</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>102</td>
<td>51</td>
<td>299</td>
</tr>
</tbody>
</table>
Table 3-3. Photovoltaic parameters of the perovskite solar cells from the highest efficiency device by more than 5 cells in each condition (with details in Tables 3-1 and Fig. 3-4).
Table 3-4. PCEs of MAPbI₃ perovskite solar cells from the sputtering, solution, and double-step deposition.

<table>
<thead>
<tr>
<th></th>
<th>Sputter</th>
<th>Solution</th>
<th>Double-Step</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>7.56%</td>
<td>5.90%</td>
<td>10.24%</td>
</tr>
<tr>
<td>2</td>
<td>8.51%</td>
<td>6.23%</td>
<td>12.31%</td>
</tr>
<tr>
<td>3</td>
<td>6.82%</td>
<td>4.37%</td>
<td>10.78%</td>
</tr>
<tr>
<td>4</td>
<td>8.96%</td>
<td>4.40%</td>
<td>9.40%</td>
</tr>
<tr>
<td>5</td>
<td>7.42%</td>
<td>6.18%</td>
<td>9.83%</td>
</tr>
</tbody>
</table>
Fig. 3-9. Device reproducibility of MAPbI$_3$ perovskite solar cells from the sputtering, solution, and double-step deposition (as shown in Table 3-3).
Fig. 3-10. Comparison of the impedance spectroscopy for differently fabricated perovskite solar cells (sputter, solution, and double-step methods) at various voltages (0.1, 0.3, 0.5, and 0.7 V under dark condition).
Fig. 3-11. Nyquist plot and equivalent circuit model (under dark condition) of the perovskite solar cells with different blocking layers (the inset presents a magnified plot for the double-step blocking layer).
Fig. 3-12. Recombination resistance ($R_{\text{rec}}$) of the perovskite solar cells under dark condition.
3.4. Conclusions

In this article, we have proposed a straightforward double-step method, consisting sputter/solution deposition to synthesize highly compact blocking layer. As a result, the deposition achieved the highest recombination resistance and PCE when it was compared with the individual sputtering or solution scheme. With the outstanding transmittance of the double-step blocking layer, the improved crystallinity and morphology of the perovskite layer provided a positive impact on the solar cell performance. We are further investigating the utilization of smaller TiO$_2$ nanoparticles and uncomplicated route to construct more efficient blocking layer for higher solar-cell efficiency.
3.5. References


Chapter 4.

An Aromatic Diamine Molecule as the A-Site Solute for Highly Durable and Efficient Perovskite Solar Cells

4.1. Introduction

Perovskite solar cells (PSCs) have been introduced with enormous attention due to its advantages of low fabrication cost and high efficiencies, with intrinsic characteristics of appropriate electronic structures, small exciton binding energy, and balanced ambipolar charge transport properties, yielding a high power conversion efficiency (PCE) of 23.3% in 2018 [1–11]. Although pioneer researches have established high PCEs which can be competitive with commercialized solar cells, device and materials stabilities of PSCs are not yet satisfactory. CH$_3$NH$_3$Pbl$_3$ (MAPbI$_3$) is one of the most studied perovskite materials, and the degradation mechanisms of MAPbI$_3$ extend to several factors. First, moisture from atmosphere destroys the perovskite structure due to the high organic reactivity of MAPbI$_3$, which implies that devices cannot operate under highly humid conditions [12–15]. Second, light is a critical degradation factor for the PSC operation. With photons absorbed, several chemical modifications occur inside the perovskite material, such as and peroxide formation, leading to degradations of the perovskite material and devices [1,15,16]. Lastly, thermally induced degradation can occur while the device is under operation conditions ($\approx$ 90 °C), because MA$^+$ in MAPbI$_3$ is sensitive
to heat energy due to its high reactivity and volatility [17–21].

To prevent the degradation of MAPbI₃, various techniques have been introduced by the modification of halide, metal, and organic substitutions. Sang Il Seok’s group introduced halide substitution with Br to obtain high stability of PSC by increased bond energy and reduced distortion of the octahedron framework [21]. Since then, various anions, such as Cl, NO₃, OAc (OAc = CH₃CH₂COO⁻), etc., have been introduced into the perovskite to reduce material defects and enhance the device stability [22–25]. Moreover, metal substitution in the perovskite has been widely investigated using Bi, Sn, Sb, etc [26–29].

While organic-cation modifications have been actively explored to improve the stability of PSCs [30–34], substitution of the cation is relatively limited due to its size within the ABX₃ lattice, sometimes leading to phase transformations from a 3D to 2D perovskite, and resulting in a high band gap and poor solar cell device performances [34–36]. Therefore, exploring an ideal cation with superior stability and device performance is a key challenge at the current stage. While passivation of imidazolium cation in perovskite has been recently reported to improve the crystallinity and light stability [37], alloying effect and device stability are to be explored and improved. Herein, we demonstrate imidazole-soluted perovskites to increase both the PCE and stability of PSCs. Imidazole (IZ) has a reasonable ionic radius of 258 pm with an aromatic structure, allowing good solid solution with MAPbI₃.

Moreover, the diammonium molecule can provide additional hydrogen
bonding for a stable material [38–40], and due to the delocalized π orbital of IZ with hydrogen bonding in a I–Pb cage, it may allow low reactivity with its surroundings leading to additional electrical conductivity. Thereby, the devices with IZ-alloyed MAPbI₃ have achieved reverse PCEs up to 20.2% with outstanding stability from light-, air-, and heat-induced environments. Furthermore, devices with IZ solute in MAPbI₃ are measured with a large active area of 2 cm² and exhibited a high PCE of 16.8%, suggesting IZ alloying is an ideal strategy for high quality devices.
4.2. Experimental Section

*Synthesis of Imidazole-Soluted Perovskite:* Imidazole (C$_3$H$_4$N$_2$, Aldrich) was mixed with a hydrogen iodide solution (Aldrich) with a 3:1 molar ratio in a round-bottom flask at 0°C for 2 h under stirring. After the solvent was evaporated at 70°C for 12 h, the precipitate was washed with diethyl ether (Daejung) for six times. The precipitate was dried at 60°C for 24 h in a vacuum oven to complete the synthesis of imidazolium iodide (C$_3$H$_5$N$_2$I).

1.5 m of imidazolium iodide and PbI$_2$ (Alfa Aesar) were mixed in N,N-dimethylformamide (DMF, Aldrich)/dimethyl sulfoxide (DMSO, Aldrich) solution (volume ratio of 9:1) to prepare the stock solution of IZ$_2$PbI$_4$. Then, 1.5 m of MAI (Solaronix) and PbI$_2$ were mixed in the DMF/DMSO solution (volume ratio of 9:1) to prepare the solution of MAPbI$_3$. Lastly, 2.5%, 5.0%, and 7.5% (molar percent) of the IZ$_2$PbI$_4$ solution were added to the MAPbI$_3$ solution to complete the preparation of the IZ-alloyed MAPbI$_3$ precursor solution.

*Device Fabrication:* For the TiO$_2$-based mesoscopic devices, fluorine-doped tin oxide substrates (FTO, TEC 8:Pilkington) were cleaned by sonication in acetone (Daejung), ethanol (Daejung), and deionized (DI) water sequentially. The TiO$_2$ blocking layer (bl-TiO$_2$) was deposited by spin-coating a mixture solution of 0.15 M titanium diisopropoxide bis(acetylacetonate) (75.0 wt% in isopropanol, Aldrich) and 1-butanol (Aldrich), and the films were annealed at 150°C for 30 min. Mesoporous TiO$_2$ (mp-TiO$_2$) paste (30NR-D, Solaronix) was diluted in ethanol (150 mg mL$^{-1}$), and then spin-coated on a bl-TiO$_2$/FTO substrate, and the films were annealed at
500°C for 60 min. For the SnO\textsubscript{2}-based planar devices, indium-doped tin oxide substrates (ITO) were cleaned with the same step as FTO. Afterwards, a SnO\textsubscript{2} colloidal particle solution (15 wt\% in water, Alfa Aesar) was diluted to 2.5\% with DI water, and then spin coated on the ITO substrate followed by annealing at 130°C for 30 min. The prepared IZ-alloyed MAPbI\textsubscript{3} solution was then spinc-oated at 3000 rpm for 20 s (with diethyl ether used as an antisolvent). The HTM was prepared by mixing 72.3 mg mL\textsuperscript{-1} of spiro-OMeTAD (Lumtec) in chlorobenzene (Aldrich) with 28.8 µL of tert-butylpyridine (Aldrich). Separately, another solution was prepared by dissolving bis(trifluoromethylsulfonyl)imide salt (Aldrich) in acetonitrile (Aldrich) with 520 mg mL\textsuperscript{-1} concentration. Then, 17.5 µL of prepared lithium bis(trifluoromethylsulfonyl)imide salt solution was transferred to spiro-OMeTAD solution to complete the preparation of hole transporting material. The solution was deposited on a film with a spin-coating method. Finally, 100 nm thick Au electrodes were thermally evaporated.

**Characterization:** The field-emission scanning electron microscope (Merlin-Compact: Carl Zeiss) was used to observe the morphologies of MAPbI\textsubscript{3}. The phases of the synthesized samples were characterized by X-ray diffraction (XRD; D8 Advance: Bruker). FTIR (Nicolet iS50: Thermo Fisher Scientific) was conducted to characterize the organic bonding nature of the perovskite. To determine the work function of IZ-soluted perovskites, UPS was measured at beamline 4D of Pohang Light Source II (PLS II), Korea. The conductivity measurements were carried out by 4-point probe (CMT-SR1000N: Chang Min Co. LTD.) on the perovskite/glass
substrate. The photocurrent–voltage (J–V) curves and steady-state current of MAPbI₃ perovskite solar cells were obtained with a potentiostat (CHI 608C; CH Instrumental Inc.) under AM 1.5 at 100 mW cm⁻² (K3000; McScience Inc.). Active area of devices were defined using Al mask with 0.09 cm² square aperture, and an Si reference cell (K801S-K15; McScience Inc.) was used for calibration. The absorbance spectra of MAPbI₃ was recorded on a UV–vis spectrophotometer (Lambda 20; Perkin Elmer, calibrated with TiO₂/glass substrate), and an external quantum efficiency (EQE) measurement system (K3100; McScience Inc.) was used to obtain the EQE spectra (calibrated with Si reference cell, S1337; Hamamatsu Photonics). Heat-induced degradation was measured with TGA (Discovery TGA: TA Instruments). Initial condition of samples and experiments were set as 25°C with ≈55% humidity in air.
4.3. Results and Discussion

Stability issues of organometallic perovskite cells are one of the major limitations for commercialization, due to the volatile and reactive nature of organic cation MA [17–19]. Imidazole (IZ) has an aromatic structure, which allows high stability due to the delocalized bonding within the molecule. Also, IZ contains diammonium network, allowing additional hydrogen bonding within the PbI$_6^{4-}$ framework (N-H-I-Pb), and can stabilize the perovskite structure [40]. However, the size of IZ$^+$ (258 pm) is larger than MA$^+$ (217 pm), possibly leading to 2D perovskite formation [37]. Previously reported large cations (phenylethylamine, ethylamine, etc.) lead to the formation of 2D perovskites with poor device performance and high band gaps [33–36]. To synthesize 3D perovskite structure, IZ should be properly alloyed with smaller molecules (MA) to satisfy Goldschmidt Tolerance Factor [41]. Additionally, recent studies suggesting the ideal design of perovskite for solar cells have shown that cation-alloyed perovskite provides improved optoelectronic behavior with the advantages of bonding and conductive nature [30,43a,b]. Likewise, IZ has diamine and aromatic framework, guaranteeing the hydrogen bonding and conductivity improvements to increase the device performance [30,42,44,45]. Therefore, IZ-alloyed MAPbI$_3$ has a potential to outperform the pristine MAPbI$_3$.

Figure 4-1 schematically illustrates the formation of IZ-based perovskite (IZ$_2$PbI$_4$) and IZ-alloyed MAPbI$_3$ (with diffraction and Fourier-transform infrared spectroscopy (FTIR) in Fig. 4-2; synthesis temperature of $\approx 60$ °C). Although
IZ$_2$PbI$_4$ exhibits a reasonable work function to operate the device, the perovskite turns into a 2D structure, and exhibits a very high band gap ($\approx 2.88$ eV) which is not suitable as a light absorbing material (Fig. 4-3). Therefore, IZ alloying (2.5%, 5.0%, and 7.5% IZ, molar percent) with MAPbI$_3$ leads to the formation of a new category of perovskite light absorbers with high stability and optoelectronic properties, while 10% of IZ has produced a secondary phase, as shown in Fig. 4-4. It should be noted that IZ was also soluted in FAPbI$_3$ and compared with the MAPbI$_3$ alloy (Fig. 4-5). As shown in Fig. 4-5, diffraction peaks of FAPbI$_3$ and MAPbI$_3$ substituted with higher content of IZ are separated into individual peaks of ABX$_3$ and IZ$_2$PbI$_4$, indicating that alloying with high content of IZ is limited. Due to the high thermodynamic barrier of FAPbI$_3$, an FA-alloyed IZ$_2$PbI$_4$ phase is likely to be produced, not IZ-alloyed FAPbI$_3$ (which is an unfavorable phase in photovoltaic research due to the production of a high band gap material).

Diffraction data confirm proper alloying of IZ in MAPbI$_3$, with increment of the lattice parameter without any secondary phases (Fig. 4-6(a); Fig. 4-7). Moreover, the FTIR peaks in Fig. 4-6(b) address the existence of IZ in the lattice. Since bond strengths of aromatic compounds are stronger than linear structures, N–H (stretch) of IZ is detected in a frequency region of $\approx 3330$ cm$^{-1}$, where the N–H (stretch) of MA is reported in a region of $\approx 3250$ cm$^{-1}$ (Fig. 4-8). Moreover, the peak intensities of C=C and N=C are also increased in a frequency region of $\approx 1580$ cm$^{-1}$ due to the presence of delocalized $\pi$ bonding in IZ. Interestingly, major peaks of MAPbI$_3$ in FTIR, C–N (stretch) at $\approx 900$ cm$^{-1}$ and NH$_3$ (bend) at $\approx 1500$ cm$^{-1}$ in
Fig. 4-8, have shifted to higher energy with IZ alloying, indicating that the bond strength of the organic cation within the perovskite structure has increased. Moreover, less volatile IZ\(^+\) (compared to MA\(^+\)) can provide better phase stabilization with reduced evaporation of organic cations (under the annealing step), while the molar ratios of carbon versus lead have dominant carbon contents when IZ is soluted in MAPbI\(_3\) (Fig. 4-9).
Fig. 4-1. Schematic illustration for structural transformations in the imidazole incorporated perovskite. Perovskite with 100% imidazole cation leads 2.9 eV of high band gap, which is not sufficient for solar-light absorber. Therefore, imidazole is soluted in CH$_3$NH$_3$PbI$_3$ to satisfy the requirements for perovskite solar cells.
Fig. 4-2. FTIR spectra and x-ray diffraction analysis for the characterization of IZ$_2$PbI$_4$. 
Fig. 4-3. Absorbance and work function of \( \text{IZ}_2\text{PbI}_4 \) on a \( \text{TiO}_2/\text{FTO} \) substrate.
Fig. 4-4. X-ray diffraction of the IZ_{0.1}MA_{0.9}PbI_{3} film.
Fig. 4-5. Identification of perovskite alloying with large IZ contents (0%, 25%, 50%, 75%, and 100%): (a) 150°C-annealed FA\(\text{PbI}_3\), and (b) 100°C-annealed MA\(\text{PbI}_3\).
Fig. 4-6. Characterization of imidazole-alloyed perovskite films with varying alloying contents of 0.0%, 2.5%, 5.0%, and 7.5%. (a) Peak shifts in X-ray diffraction scans and effect on the lattice parameter ($a = b$ in tetragonal phase). (b) Relative transmittance of imidazole-alloyed MAPbI$_3$ through FTIR.
Fig. 4-7. X-ray-diffraction characterization of IZ-alloyed perovskite (0.0%, 2.5%, 5.0%, and 7.5%) in MAPbI$_3$. 
Fig. 4-8. Transmittance of imidazole-alloyed MAPbI$_3$ using FTIR (with major peaks of MAPbI$_3$ labeled).
Fig. 4-9. Atomic ratio of carbon and lead by EDS at different IZ contents in MAPbI₃, compared to the ideal concentration (dashed line).
After IZ is successfully alloyed in MAPbI$_3$, optical properties and grain sizes are analyzed in Fig. 4-10(a) and (b). While all the alloyed perovskites exhibit similar band gap, the highest absorption coefficient is obtained with the 2.5%-IZ alloying, which is correlated with the grain size (with scanning electron microscope (SEM) images illustrated in Fig. 4-11). We believe that IZ has not only increased the unit cell volume, but also possibly formed a 2D/3D hybrid structure, resulting in smaller grain sizes when the IZ content is higher than 2.5% [43(a,b)]. The aromatic structure of IZ is more electrically conductive than linear ones [43], leading to the enhanced electrical conductivity by the incorporation of IZ, as shown in Fig. 4-11(c) (also in Fig. 4-12), which guarantees sufficient charge transport and device operation. Furthermore, ultraviolet photoelectron spectroscopy (UPS) was conducted to understand the electronic structures of IZ-alloyed MAPbI$_3$ (Fig. 4-11(d)). The work function decreases with the addition of IZ, which can provide a positive effect resulting in the increased open-circuit voltage ($V_{oc}$).

Devices with different contents of IZ alloying in MAPbI$_3$ are analyzed to demonstrate the effect of IZ on the solar cell performance by using a TiO$_2$-based mesoscopic device structure. The $J$–$V$ curve with 2.5% IZ exhibits the highest PCE of 17.6 ± 0.3% by more than ten cells (Fig. 4-13(a)) (with the minimized $J$–$V$ hysteresis from the 2.5%-IZ-soluted device in Fig. 4-14). Even though samples with 5.0% and 7.5% of IZ have also revealed promising improvements (with $\eta$ = 17.0% and 14.7%, respectively), the enhanced electrical and optical properties have allowed the highest PCE with 2.5% IZ. (Median PCE values are presented above,
and reproducibility of devices are illustrated in Fig. 4-15 (scan rate = 10 mV s\(^{-1}\)). The EQE results in Figure 4b again confirm the highest efficiency from improved carrier transport, and the integrated currents of all devices get close to their short-circuit current values.

Device stability under degrading conditions is another critical issue for practical perovskite solar cells. Air stability was tested for 30 days (≈ 55% relative humidity, without encapsulation) under dark (Fig. 4-13(c)), and as confirmed in Fig. 4-6 (proper alloying) and Fig. 4-8 (bonding nature), nonvolatile and strongly-bonded IZ molecules protect the devices under the open O\(_2\) and H\(_2\)O degradation conditions [12–14]. Interestingly, Fig. 4-16 illustrates the diffraction of IZ-soluted perovskite films after 30 days, and it shows traces of IZ\(_2\)PbI\(_4\) when 5.0% or 7.5% of IZ is soluted in MAPbI\(_3\). It is very exciting that small amounts of IZ\(_2\)PbI\(_4\) do not significantly reduce the device stability. The voltage- and light-induced degradation is also tested for 1000 s (Fig. 4-13(d), measured in air without encapsulation), due to the halide migration and electron/hole-transport layers [1, 15, 16]. Devices with 2.5%, 5.0%, 7.5% of IZ-alloyed MAPbI\(_3\) exhibit ≈ 80%, ≈ 85%, and ≈ 90% of the initial current, where the unalloyed device has only sustained ≈ 60%, again confirming the stability of IZ alloying in MAPbI\(_3\). Moreover, thermal stability of perovskite solar cells is measured at 100°C for 6 h (Fig. 4-13(e) and 4-17), heated in air without encapsulation). It should be noted that normal operating temperature of solar cells is ≈ 70°C [46]. However, devices heating in air could be damaged by several factors, such as heated H\(_2\)O and O\(_2\). Therefore, experiment is designed to an extreme
condition (100°C) to maximize the heat-induced environment within short time in air. In order to confirm the nonvolatile nature of IZ (boiling temperature of ≈ 240°C) and strong bonding of IZ within the PbI$_6^{4-}$ framework, bare and IZ alloyed perovskite powder are further analyzed with thermogravimetric analysis (TGA). Figure 4-18 confirms that IZ-alloyed perovskite retains the robust perovskite nanostructures from the heat. While the absence of IZ in MAPbI$_3$ is one major reason in the PCE reduction, Fig. 4-19 additionally confirms that there are visible deformations in hole-transport material (HTM) and Au.

For higher performance and stability, architectural modification of the device with SnO$_2$ (instead of TiO$_2$ as the electron transport layer for higher electron mobility) [15,16,47] is adapted, exhibiting an improved reverse PCE of 20.2% with a forward PCE of 19.0% in a planar structure, as shown in Figure 4f. Also, this device exhibits high stability over 120 s under steady-state current conditions. Moreover, a large area device [48] (cell area: 2 cm$^2$) is tested with 2.5% IZ, exhibiting a PCE of 16.8%, and the device stability is confirmed over 120 s under steady-state current conditions in Fig. 4-20. We believe that the aromatic molecule comprised of a multiamine-based cation can be one leading strategy for highly stable- and efficient perovskite solar cells.
Fig. 4-10. Optical and electronic characteristics of imidazole-alloyed MAPbI₃ films. (a) Band gap change, (b) grain-size distributions, (c) electrical conductivity, and d) work function.
Fig. 4-11. SEM images of different IZ contents in MAPbI$_3$. 
Fig. 4-12. Electrical conductivity of films with various IZ contents in MA$\text{PbI}_3$
(with 100% indicating I$\text{Z}_2\text{PbI}_4$).
Fig. 4-13. Device performance and stability Test. (a) J–V curves (scan rate of 10 mV s$^{-1}$) and b) EQE spectra of imidazole-alloyed MAPbI$_3$. (c) Degradation of devices up to 30 days when cells are stored in air ($\approx$ 55% humidity and dark). (d) Steady-state current for a 1000 s time scale to confirm the light- and voltage-induced degradation of the solar cells. (e) Heat-induced degradation of devices under 100°C for 6 h. (f) J–V curve of the champion device in this study (with 2.5% imidazole, and forward and reverse J–V shown as dotted and solid lines, respectively) and its steady-state current (at 0.90 V) using a SnO$_2$/ITO substrate.
Fig. 4-14.  $J$-$V$ curves for various contents of imidazole-alloyed MAPbI$_3$ (dotted and solid lines for forward and reverse scans, respectively) on TiO$_2$/FTO substrates.
Fig. 4-15. Reproducibility of perovskite solar cells for various contents of imidazole-alloyed MAPbI$_3$ on TiO$_2$/FTO substrates.
Fig. 4-16. X-ray-diffraction characterization of perovskite films after 30 days in air.
Fig. 4-17.  $J$-$V$ curves of fresh vs. aged (100°C for 6 h) devices.
Fig. 4-18. Thermogravimetric analysis (TGA) for characterization of the thermal stability of perovskite powders.
Fig. 4-19. Cross-sectional and plan-view SEM images for fresh and thermal-induced devices (100°C for 6 h).
Fig. 4-20. $J$–$V$ curve and steady-state current results with a large active area of 2 cm$^2$ (2.5% imidazole) by using a SnO$_2$/ITO substrate.
4.4. Conclusions

Although perovskite solar cells have gathered enormous attention as next generation photovoltaics, stability issues should be resolved for future commercialization to become possible. Here, we straightforwardly introduced IZ as an attractive cation solute to obtain both high PCE and stability of the devices. Due to the unique properties, such as the aromatic and diamine network of IZ, it exhibited superior stability with improved electronic structures, allowing phase stabilization, and high electrical/optical properties. Also, devices with a large active area of 2 cm$^2$ exhibited PCEs as high as 16.8%. This facile diamine-based cation-alloying technique integrated into the well-known MAPbI$_3$ perovskite surely improved several critical requirements that the device requires to be practical for future potential photovoltaics.
4.4. References


Chapter 5.

Origins of Efficient Perovskite Solar Cells with Low-Temperature Processed SnO$_2$ Electron Transport Layer

5.1. Introduction

Organometal halide perovskite (OHP) is regarded as one of the most promising candidate for next-generation photovoltaic materials in the aspects of both cost and efficiency. Intense research on the applications of OHP to solar cell has achieved remarkable progress, increasing the power conversion efficiency (PCE) up to $\sim 23\%$ in just several years, as a result of accomplishments in the compositional engineering and morphology/crystallization control of OHP [1-3]. Recent studies have improved both the photovoltaic property and stability of perovskite solar cells by modifying and optimizing the perovskite films [2-8]. However, limitations still remain within the conventional electron/hole transport layers (ETL/HTL) and interfaces, and so does demand for further advances [9].

The perovskite solar cell (PSC) with current world-record efficiency adopts mesoscopic TiO$_2$ as an electron-transport layer. Though mesoscopic structure of TiO$_2$ can boost electron extraction from the perovskite layer to anode, it has a drawback requiring high-temperature process around $500^\circ$C that hinders the commercialization of PSC [10-13]. On the other hand, planar PSC requires simple and economic fabrication processes compared to the mesoscopic PSC, and thus has
attracted huge attention [14-16]. For planar PSC, SnO₂ film has been recently noticed to be one of the most promising ETL with high charge mobility and low photoactivity [17-22].

Several researches have observed the effect of SnO₂ annealing temperature on the solar cell performance [23-25]. For example, Fang et al. fabricated SnO₂-based ETL by spin-coating SnCl₂ precursor solution at several temperatures (185-500°C), and Docampo et al. used ALD-processed SnOₓ ETL (room temperature (RT) to 300°C) appointing the Fermi-level change to be an origin of the device properties [23,24]. Nevertheless, the exact correlation between the SnO₂-film characteristics and solar-cell performance are not yet fully understood, especially with nanoparticle-based SnO₂ ETL.

In this work, dependence of the device performance on the SnO₂ annealing temperature is observed with n-i-p planar PSCs using nanoparticle-based SnO₂ layer as an ETL. In order to understand the annealing effects on the SnO₂ properties and declare the factors contributing to the photovoltaic performance, nanoscopic morphology and optical/electronic properties of SnO₂ films are scrutinized with various annealing temperatures (RT to 200°C). In addition, because the solar cell performance is strongly correlated to various factors including the properties of perovskite, electron/hole transporting materials, and interfaces [9,26-34], the deep-trap states and band alignment are also discussed. With explication on how SnO₂ annealing temperature affects the film property and sequentially the solar cell performance, insights to realize efficient perovskite solar cell with low-temperature process are provided, expanding the perspective of its commercial applications.
5.2. Experimental Section

**SnO\(_2\) Film Deposition.** ITO substrate (Wooyang GMS) was etched by zinc powder (TCI Chemicals) and cleansed under sonication in acetone, ethanol, and deionized water. The substrate was used after 15 min of UV-ozone treatment. In order to prevent agglomeration of nanoparticles, 15 wt% SnO\(_2\) nanoparticle dispersion in H\(_2\)O (Alfa-Aesar) was stirred and sonicated before dilution. Then the suspension was diluted to 3.4 wt %, filtered by PTFE membrane (CHMLAB), and spin-coated on the ITO substrate at 3000 rpm for 30 s. Subsequently, SnO\(_2\) layer was annealed at various temperature (RT, 80°C, 120°C, 160°C, and 200°C) for 30 min on a hot plate, and UV-ozone treated for 15 min afterward.

**Solar Cell Fabrication.** For the Cs\(_{0.05}(\text{FA}_{0.83}\text{MA}_{0.17})_{0.95}\text{Pb}(\text{I}_{0.83}\text{Br}_{0.17})_3\) perovskite (CsFAMA) film, 1.3 M (FA\(_{0.83}\text{MA}_{0.17})\text{Pb}(\text{I}_{0.83}\text{Br}_{0.17})_3\) perovskite precursor solution was prepared by dissolving formamidinium iodide (FAI; Great Solar Laboratory), methylammonium bromide (MABr; Great Solar Laboratory), lead iodide (PbI\(_2\); TCI Chemicals), and lead bromide (PbBr\(_2\); TCI Chemicals) in a mixture of N,N-dimethylformamide (DMF; Sigma-Aldrich) and dimethyl sulfoxide (DMSO; Sigma-Aldrich) with the volume ratio of 4:1. For Cs doping, 1.0 M CsI (TCI Chemicals) solution dissolved in the same solvent was added. The perovskite solution was stirred for 2 h and then spin-coated on the as-prepared SnO\(_2\) layer in two steps of spinning program: 1000 rpm for 10 s for the first step and 5000 rpm for 20 s for the second step. Three hundred microliters of chlorobenzene (Sigma-Aldrich) was dropped 3 s before the second spin-step ended, and the substrate was annealed at
100°C for 30 min on a hot plate. Hole transporting material was prepared by dissolving 72.3 mg of spiro-MeOTAD (Lumtec) in 1 mL of chlorobenzene (Sigma-Aldrich), and 28.8 μL of 4-tert-butylpyridine (Sigma-Aldrich) and 17.5 μL of bis(trifluoromethane)sulfonimide lithium salt (SigmaAldrich) in acetonitrile (520 mg/mL) were added as additives. The HTM solution was spin-coated on the substrate, and finally Au electrode was thermally evaporated.

Characterization. The surface topography of SnO₂ layer was observed by using atomic force microscopy (NX-10; Park Systems). Each measurement was conducted for the area of either 1 × 1 μm² or 10 × 10 μm². Four-point probe was utilized to measure electric conductivity of SnO₂ films deposited on a glass substrate. Work function and valence band maximum of each deposited SnO₂ layer were measured via multipurpose X-ray photoelectron spectroscopy (Sigma Probe; Thermo VG Scientific) with argon sputtering. Light with energy $hν = 21.22$ eV was used in the ultraviolet photoelectron spectroscopy (UPS) measurement. Optical properties of SnO₂ films were measured with UV/vis spectroscopy (V-770; JASCO) with an integrating sphere. Incident photon to current efficiency (IPCE) measurements were performed by solar cell IPCE system (K3100; McScience). Photocurrent density-voltage ($J-V$) curves were achieved via solar cell measurement system (K-3000; McScience) for an active area of 0.09 cm². During the measurement, the voltage was swept from the reverse to forward direction (from 1.2 to 0.1 V with a scan rate of 100 mV/s). One sun light was illuminated using a solar simulator (xenon lamp, air mass 1.5 G). For impedance analysis, a potentiostat (Zive SP-1; WonATech)
was adopted, and the impedance of photovoltaic device was measured with 10 mV AC perturbation in the frequency range from 10 mHz to 100 kHz under zero bias in dark condition. Before this measurement, all the devices had been relaxed in the dark until voltage drops below 3 mV [35]. To observe film morphology of perovskite layers and cross-sectional image of devices, a field-emission scanning electron microscope (Merlin Compact; Zeiss) was used. Crystal structures were examined by an X-ray diffractometer (New D-8 Advance; Bruker).
5.3. Results and Discussion

To investigate the effect of SnO$_2$ annealing temperature on the solar cell performance, SnO$_2$ films are annealed at various temperatures with the resultant cell parameters including power-conversion efficiency ($\eta$), open-circuit voltage ($V_{OC}$), fill factor ($FF$), short-circuit current density ($J_{SC}$), and hysteresis index ($HI$) (Fig. 5-1). Though the optimum annealing temperature of nanoparticle-based SnO$_2$ ETL has been previously regarded to exceed 150°C [18,21], the most efficient solar cell is acquired at 120°C with the highest $\eta$ of 19.0%. The $\eta$ presents a trend of arch upward, and it is mainly attributed to the $V_{OC}$ and $FF$ that show similar dependences with peaks at the 120°C condition as well (Fig. 5-1(a-c)). Interestingly, the low-temperature processed SnO$_2$ annealed below 150°C or even at RT outperforms the high-temperature processed SnO$_2$ in the aspects of $V_{OC}$, $FF$, and consequently $\eta$. Furthermore, as shown in Fig. 5-1(d), the $J_{SC}$ is measured to increase as SnO$_2$ annealing temperature decreases. This annealing effect on $J_{SC}$ is consistent with the IPCE measurement in Fig. 5-2, of which the integrated $J_{SC}$ also increases with the lower-temperature processed SnO$_2$. On the other hand, hysteresis is reduced for the SnO$_2$ ETLs annealed at lower temperatures (Fig. 5-1(e)). The $J$-$V$ curve of a champion cell for each annealing condition is shown in Fig. 5-3(a,b) with the corresponding cell parameters referred in Table 5-1. The upper layers including perovskite layer, HTL, and metal electrode are fabricated by the same procedures. The differences in both crystallinity and microscopic morphology of perovskite upper layers are also negligible (Figs. 5-4 and 5-5), and thereby we assume that these
observed tendencies in Fig. 5-1 originate only from the features of SnO$_2$ ETL and its interface. Further analyses on the SnO$_2$ films and interfaces are conducted to understand the correlation between their properties and the solar cell performance, as well as to reveal the origins of outstanding performance by low-temperature processed SnO$_2$ ETL.
Fig. 5-1. Device performance versus SnO$_2$ annealing temperature. (a) $\eta$, (b) $V_{OC}$, (c) $FF$, (d) $J_{SC}$, and (e) $HI = (\eta_{rev} - \eta_{for})/\eta_{rev}$ of solar cells as a function of SnO$_2$ annealing temperature. Each data point demonstrates the representative device of one experimental batch. (f) $J$-$V$ curves of champion cells at room temperature and 120°C with the cell geometry by SEM (CsFAMA = Cs-doped (FA$_{0.83}$MA$_{0.17}$)Pb(I$_{0.83}$Br$_{0.17}$)$_3$).
Fig. 5-2. IPCE spectra of the perovskite solar cells. The IPCE measurements of PSCs with various SnO$_2$ annealing temperatures. The integrated $J_{SC}$ are indicated.
Fig. 5-3. $J$-$V$ curve of the champion cell for each SnO$_2$ annealing temperature. Solar cells are examined by (a) reverse scan and (b) forward scan, respectively. The corresponding cell parameters are referred in Table 5-1.
Table 5-1. Device performance vs. SnO$_2$ annealing temperature. Short-circuit current ($J_{sc}$), open-circuit voltage ($V_{oc}$), fill factor ($FF$), and power-conversion efficiency ($\eta$) of the champion cells (reverse direction). Full $J$-$V$ characteristics are shown in Fig. 5-3.

<table>
<thead>
<tr>
<th>Annealing Temperature</th>
<th>$J_{sc}$ (mA cm$^{-2}$)</th>
<th>$V_{oc}$ (V)</th>
<th>$FF$ (%)</th>
<th>$\eta$ (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>$RT$</td>
<td>21.8</td>
<td>1.084</td>
<td>76.7</td>
<td>18.1</td>
</tr>
<tr>
<td>80$^\circ$C</td>
<td>21.6</td>
<td>1.098</td>
<td>77.6</td>
<td>18.4</td>
</tr>
<tr>
<td>120$^\circ$C</td>
<td>22.0</td>
<td>1.098</td>
<td>78.5</td>
<td>19.0</td>
</tr>
<tr>
<td>160$^\circ$C</td>
<td>21.2</td>
<td>1.038</td>
<td>76.2</td>
<td>16.8</td>
</tr>
<tr>
<td>200$^\circ$C</td>
<td>20.9</td>
<td>1.026</td>
<td>70.1</td>
<td>15.0</td>
</tr>
</tbody>
</table>
Fig. 5-4. X-ray diffraction patterns of perovskite solar cells, with and without HTL/Au. XRD patterns of (a) full devices and (b) perovskite films, fabricated on a SnO$_2$ layer annealed at various temperatures. Peaks are indexed assuming perovskite crystal in a cubic structure. The diamond and asterisk symbols represent the peak positions of PbI$_2$ and ITO, respectively.
Fig. 5-4. SEM images of perovskite film surfaces. Surface morphology of perovskite film deposited on a SnO2 layer annealed at (a) RT, (b) 80°C, (c) 120°C, (d) 160°C, and (e) 200°C.
First, the surface morphology of SnO$_2$ film has been observed to understand how uniformity of the surface changes by the annealing condition and affects the solar cell performance. Considering the size of SnO$_2$ nanoparticles (3-5 nm) [18] and thickness of film ($\sim$ 20 nm in Fig. 5-6(a)), surface morphology has been observed in nanoscale using atomic force microscopy (AFM) rather than scanning electron microscopy (SEM) (Fig. 5-6(b)). Topographies of bare ITO and various SnO$_2$ films are shown in Fig. 5-7(a-f). In general, the deposited SnO$_2$ films demonstrate considerably smoother surface than bare ITO, confirming that SnO$_2$ nanoparticle layers are successfully formed regardless of the annealing temperature. In addition, the surface roughness is measured quantitatively in peak-to-valley average and root-mean-squared value ($\sigma_{\text{rms}}$), respectively (Fig. 5-7(g)), confirming that the SnO$_2$ nanoparticle layer shapes more uniformly and smoothly when annealed at lower temperature below 150°C. The $\sigma_{\text{rms}}$ for SnO$_2$ annealed at 160 and 200°C are larger than 0.8 nm in average, while those of low-temperature processed SnO$_2$ are $\sim$ 20% smaller. Similarly, the peak-to-valley roughnesses soar at 160 and 200°C.

The morphology of SnO$_2$ nanoparticle layer depends on its annealing temperature, and the rate of solvent evaporation is presumed to be responsible. Regarding that the thickness of deposited SnO$_2$ layer is observed to be $\sim$ 20 nm, the measured roughnesses of SnO$_2$ annealed at 160 and 200°C are of notable scale to deteriorate the contact with perovskite upper layer by forming shunting paths such as pinholes. It is well known that the charge collection efficiency and the shunt resistance of solar cells are deeply involved with nanoscopic morphology of ETL and the formation of shunting paths [20,22,36,37], and hence the uniformity of SnO$_2$
ETL is expected to influence both $J_{SC}$ and $FF$ of the perovskite solar cell. Accordingly, the rough surface of high-temperature processed SnO$_2$ is reproached for its reduced $J_{SC}$ and $FF$. Though the electrical conductivity is greater for higher annealing temperature (Fig. 5-7(h)), it seems not critical for the charge transport within only $\sim$ 20 nm thick ETL.

To further scrutinize the correlations between the annealing temperature of SnO$_2$ and cell parameters, work function and valence band maximum (VBM) of SnO$_2$ are evaluated from the secondary electron edge and valence band spectrum (Figs. 5-8(a,b), respectively). As SnO$_2$ annealing temperature increases, the work function of SnO$_2$ film first rises from 4.14 eV at RT to 4.39 eV at 120°C, and then drops to 4.19 eV at 200°C. The VBM with respect to the Fermi level ($VBM = E_{\text{offset}} - E_F$) is observed to increase as SnO$_2$ annealing temperature decreases. To compare the band diagrams, the optical bandgap of each SnO$_2$ film was measured (shown in Fig. 5-8(c)), exhibiting from 3.96 to 3.92 eV as the annealing temperature increases from RT to 200°C. The band diagrams of SnO$_2$ films depicted in Fig. 5-8(d) (based on the values of Table 5-2) indicates that the high-temperature processed SnO$_2$ has relatively high conduction band maximum (CBM) with the perovskite upper layer. With the driving force of electron extraction from the perovskite layer to ETL, the low-temperature processed SnO$_2$ is likely to exhibit more preferred band alignment in short-circuit condition for efficient electron transport (Fig. 5-1(d)).

Observing the shifts of band levels, we suspect that the defect formation, especially at the ETL/perovskite interface, also depends on the SnO$_2$ annealing temperature. To explore the defects of SnO$_2$-based solar cells, the impedance
analysis is performed for capacitance as $C \equiv 1/\omega Z$ (Fig. 5-9). The capacitive feature of perovskite solar cell at high frequency is determined by geometrical and depletion-layer capacitance of perovskite [38,39], whereas the low-frequency capacitance is claimed to originate from the charging/discharging of electronic traps at the interfaces [40-43]. In Fig. 5-9(a), the capacitances at high frequency over 100 Hz are almost indistinguishable, but on the other hand the low-frequency capacitances show clear differences depending on the SnO$_2$ annealing temperature. Considering that the fabrication procedures except for the SnO$_2$-annealing temperatures are identical for the examined devices, the differences in the low frequency capacitances reflects the contributions of only from the ETLs and/or ETL/perovskite interfaces, rather than other constituents such as perovskite layers and HTLs. This argument is also supported by the analyses including X-ray diffraction and SEM on the perovskite layers with negligible differences (Figs. 5-4 and 5-5).

Deep-level traps at the interfaces contribute to the device capacitance under low-frequency perturbation by being charged and discharged repeatedly [40,44,45]. From the capacitance-frequency plot, the trap-density state $n_t$ versus $E_{\text{on}}$ ($= E - E_{\text{band edge}}$) can be calculated [45,46]. In Fig. 5-9(b), $n_t$ for different SnO$_2$ annealing temperatures are compared and the deep-trap distribution noticeably varies, indicating that the defect formation at the interface between the SnO$_2$ ETL and perovskite layer is influenced by the SnO$_2$-annealing temperature. From the Gaussian fitting of trap-density state, the trap density ($N_t$) and trap level ($E_0$) have been evaluated quantitatively (Fig. 5-9(c) and Table 5-3). As shown in Fig. 5-9(c),
$N_t$ draws an arch downward with the lowest trap density at 120°C, of which the trend is opposite to that of the observed $V_{oc}$.

These results confirm that the interfacial deep-traps play a significant role determining the $V_{oc}$ of the solar cell, and the schematics are in Fig. 5-9(d). When PSC is illuminated, the photogenerated electrons fill the electronic traps, and when an electron is trapped in a deep-level state, a nonradiative recombination process is likely to occur. The recombination is believed to be the main factor undermining $V_{oc}$ of the solar cell, which is verified by these SnO$_2$ devices with low Nt exhibiting high $V_{oc}$ and vice versa (Fig. 5-9(c)). Various defects in the perovskite solar cells are the main reasons causing $J$-$V$ hysteresis or irreversible degradation in the device performance. Plausibly, the low-temperature processed SnO$_2$ devices demonstrate small hysteresis effects, and their reduced traps are thought to be one of the reasons. Yet, other factors including shallow-traps are also underlying, making tendency of hysteresis slightly different with that of the interfacial deep-traps (Figs. 5-1(e) and 5-9(c)). Meanwhile, as we have tested the thermal stability of the as-fabricated devices, these less-defective solar cells with SnO$_2$ annealed at 120°C sustain 90% of their initial PCEs after being kept in the 85°C/ 85% relative-humidity (RH) environment for over 300 h, as shown in Fig. 5-10. Deeper studies are to be performed on these stability results, including the roles of various traps at each layer and interfaces in the long term degradation mechanisms.
Fig. 5-6. Basic characterizations of SnO$_2$ thin films. (a) Cross-sectional SEM image of the device (ITO/SnO$_2$/CsFAMA/spiro/Au) with a thickness estimation of SnO$_2$ layer. (b) Planar SEM image and (c) AFM topography of bare ITO and ITO/SnO$_2$ surfaces. The AFM images are shown in the same color scale. For (b) and (c), SnO$_2$ films are characterized before and after annealing at 120°C.
Fig. 5-7. Morphological features and electrical properties of SnO$_2$ films. Surface topography of (a) bare ITO substrate, and (b-f) SnO$_2$ layer annealed at different temperatures. The AFM images are shown in the same color scale. (g) Roughnesses by peak-to-valley and root-mean-squared values as a function of annealing temperature with bare ITO as a reference. (h) Electric conductivity of SnO$_2$ thin films.
Fig. 5-8. Energy level diagram of SnO₂ electron-transport layer. (a) Secondary electron edge and (b) valence-band maximum of SnO₂ layer at each annealing temperature (as measured by UPS). (c) Tauc plot of SnO₂ films for the bandgap energy ($E_g$). The blue arrow indicates the shift of bandgap as the annealing temperature increases (Detailed fitting parameters for panels a-c are in Table 5-3). (d) Schematic band diagram of each SnO₂ layer with the perovskite as a reference.
Table 5-2. Work function, valence band maximum, and bandgap of each SnO\textsubscript{2} layer.

<table>
<thead>
<tr>
<th>Annealing Temperature</th>
<th>Work Function (eV)</th>
<th>VBM (eV)</th>
<th>$E_g$ (eV)</th>
</tr>
</thead>
<tbody>
<tr>
<td>RT</td>
<td>4.14</td>
<td>-3.56</td>
<td>3.96</td>
</tr>
<tr>
<td>80°C</td>
<td>4.25</td>
<td>-3.56</td>
<td>3.96</td>
</tr>
<tr>
<td>120°C</td>
<td>4.39</td>
<td>-3.53</td>
<td>3.95</td>
</tr>
<tr>
<td>160°C</td>
<td>4.23</td>
<td>-3.45</td>
<td>3.94</td>
</tr>
<tr>
<td>200°C</td>
<td>4.19</td>
<td>-3.41</td>
<td>3.92</td>
</tr>
</tbody>
</table>

Fermi level of SnO\textsubscript{2} film is calculated from $E_F$ (= work function) = $h\nu$ - $E_{cutoff}$ with $h\nu = 21.22$ eV. Bandgap of SnO\textsubscript{2} has been estimated from the Tauc plot in Fig. 5-8(c).
Fig. 5-9. Effects of annealing temperature on the electronic trap states. (a) Capacitance-frequency plot and (b) trap distribution spectra of solar cells. (c) Trap density per volume ($N_t$) and $V_{OC}$ of each solar cell. $N_t$ is obtained by fitting the trap density state in (b) using a Gaussian function. (d) Schematics for the role of interfacial traps in recombination.
<table>
<thead>
<tr>
<th>Annealing Temperature</th>
<th>Trap Density $N_t$ (cm$^{-3}$)</th>
<th>$E_0$ (eV)</th>
</tr>
</thead>
<tbody>
<tr>
<td>RT</td>
<td>$4.30 \pm 0.08 \times 10^{17}$</td>
<td>0.602</td>
</tr>
<tr>
<td>80°C</td>
<td>$4.20 \pm 0.07 \times 10^{17}$</td>
<td>0.601</td>
</tr>
<tr>
<td>120°C</td>
<td>$4.05 \pm 0.02 \times 10^{17}$</td>
<td>0.605</td>
</tr>
<tr>
<td>160°C</td>
<td>$4.40 \pm 0.07 \times 10^{17}$</td>
<td>0.613</td>
</tr>
<tr>
<td>200°C</td>
<td>$4.63 \pm 0.10 \times 10^{17}$</td>
<td>0.615</td>
</tr>
</tbody>
</table>

Table 5-3. Electronic trap density and defect energy level $E_0$ (Fig. 5-9).
Fig. 5-10. Thermal stability of perovskite solar cells. Stability of encapsulated perovskite solar cells with SnO$_2$ ETL annealed at 120°C, stored in 85°C environment with 85% relative humidity (RH) in dark. Two devices are shown in a normalized PCE (reverse scan).
5.4. Conclusions

Uniform electron-transport layer using SnO$_2$ nanoparticles is systematically investigated. By varying the annealing temperature from RT to 200°C, the best efficiency of 19.0% has been obtained from annealing at 120°C. The morphological, optical, and electronic properties of SnO$_2$ layers are investigated, and the interfacial trap states between SnO$_2$ and perovskite layers are analyzed. Efficient perovskite solar cells with low-temperature processed SnO$_2$ ETL are realized by uniform/smooth SnO$_2$ surface, favorable band alignment, and reduced trap density plus shifting toward the bandedge. These less-defective solar cells can sustain 90% of their initial PCEs from the 85°C/85%-RH environment for over 300 h. Our straightforward work offers insights to realize more efficient and stable perovskite solar cells with lower cost, enlarging the potential of commercial applications.
5.5. References


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Chapter 6.

Triamine-Based Aromatic Cation as a Novel Stabilizer for Efficient Perovskite Solar Cells

6.1. Introduction

Organometallic perovskite is one of the most popular research areas, and the solar cell application of perovskite materials is gaining enormous attention with the rapid growth. Throughout the extensive work, the power conversion efficiency (PCE) of perovskite solar cells is soaring up to 24.2%, and the stabilities are gradually improving [1,2]. Even though the PCE of the perovskite solar cell is already comparable to those of commercial demands, the stability is not satisfactory enough to replace the conventional photovoltaics.

Perovskite solar cells are generally designed to have device architectures of either p-i-n or n-i-p type. The perovskite layer (i) plays very important role as the main light absorber, but it is highly reactive under heat, humidity, and light. Although n- or p- type carrier transport layers of metal oxides, polymers, or small molecules also count for device properties [3-16], stabilizing the perovskite itself is the most important to realize stable solar-cell device. It is well known that triple-cation perovskite \( \text{Cs}_{0.05}(\text{FA}_{0.85}\text{MA}_{0.15})_{0.95}\text{Pb}(\text{I}_{0.85}\text{Br}_{0.15})_{3} \), where FA is (NH\(_2\))\(_2\)CH\(^+\) and MA is CH\(_3\)NH\(^+\) is one of the most stable perovskite materials [17-20]. However, FA and MA are
highly reactive under heat, humidity, and light, requiring additional modification to further improve the quality of perovskite [5,21-25].

Although the organic-based p-type materials (the most common one for the perovskite solar cells: spiro-OMeTAD) can have a stability problem [26,27], recent researches have revealed that ion doping or alloying of perovskite can largely improve the device stability, compensating the stability issues of spiro-OMeTAD. In more detail, metal-halide doping or organic alloying surely help the device stability by forming a strong bonding within the lattice or passivating the defects [5,9,25,28-33]. The surface passivation on the perovskite is also introduced as an effective method to reduce the degradation of materials, even though it only stabilizes the interface, and the bulk properties of perovskite may still remain unstable [34-36]. Therefore, the doping or alloying of perovskite is highly practical and straightforward method to improve the materials stability, and thereby the performance of solar cells.

Herein, we introduce 1,2,4-triazole (C$_2$H$_3$N$_3$) as a cation solute in triple-cation perovskite, since 1,2,4-triazole is an aromatic compound that is extremely stable compared to FA or MA [37-41]. 1,2,4-triazole is a triamine-based aromatic compound, having a strong interaction within the perovskite structure, and also improving the charge transport behavior of cation site of the perovskite [5,42-47]. However, because of its relatively large size (~258 pm), 1,2,4-triazole in perovskite is limited to a small amount in order to maintain satisfactory tolerance factor [48]. By optimizing the content of 1,2,4-triazole alloy, the optical and electronic properties are improved boosting the PCE up to 20.9%. Furthermore, the thermal stability of the solar cell is confirmed under the extreme condition (85°C/85% relative humidity (RH)) for 700 h to address the optimum strategy of perovskite and device stabilization.
6.2. Experimental Section

**Synthesis of Triazole-Soluted Perovskite:** 1,2,4-triazole (C$_2$H$_3$N$_3$; Sigma-Aldrich) was mixed with hydrogen iodide solution (HI, Sigma-Aldrich) with 3:1 molar ratio in a round-bottom flask at 0°C for 2 h under stirring. After the solvent was evaporated at 70°C for 12 h, the precipitate was washed with diethyl ether (Daejung) for ten times. The precipitate was dried at 60°C for 24 h in a vacuum oven to complete the synthesis of triazolium iodide (C$_2$H$_4$N$_4$I).

For the perovskite film, 1.8 M Cs$_{0.05}$(FA$_{0.85}$MA$_{0.15}$)$_{0.95}$Pb(I$_{0.85}$Br$_{0.15}$)$_3$ perovskite precursor solution was prepared by dissolving formamidinium iodide (FAI; Great Solar Laboratory), methylammonium bromide (MABr; Great Solar Laboratory), lead iodide (PbI$_2$; TCI Chemicals), lead bromide (PbBr$_2$; TCI Chemicals), and cesium iodide (CsI; Great Solar Laboratory) into a mixture of N,N-dimethylformamide (DMF; Sigma-Aldrich) and dimethyl sulfoxide (DMSO; Sigma-Aldrich).

To prepare the 1,2,4-triazole-alloyed perovskite, 1.8 M of stock solution of 1,2,4-triazolium perovskite was made by mixing triazolium iodide, PbI$_2$, and PbBr$_2$ into DMF:DMSO mixture solution to make a TAPbI$_{0.85}$Br$_{0.15}$ (100% of triazol cation, where TA indicates triazolium ion), then the completed stock solution was stoichiometrically diluted (0, 2, 4, or 6 mol. %) in a solution of prepared Cs$_{0.05}$(FA$_{0.85}$MA$_{0.15}$)$_{0.95}$Pb(I$_{0.85}$Br$_{0.15}$)$_3$.

**Device Fabrication:** Indium-doped tin oxide (ITO; AMG) was cleaned under sonication in acetone, ethanol, and deionized water. Then SnO$_2$ was spin-coated on
a cleaned substrate with the previously developed method. The perovskite solution was sonicated for 30 min, and then spin-coated on the as-prepared SnO\textsubscript{2} layer in two steps of spinning program: 500 rpm for 5 s for the first step and 5000 rpm for 20 s for the second step. 1 mL of diethyl ether (Daejung) was dropped 5 s before the second spin-step ended, and the substrate was annealed at 105°C for 40 min on a hot plate. Hole transporting material was prepared by dissolving 72.3 mg of spiro-OMeTAD (Lumtec) in 1 mL of chlorobenzene (Sigma-Aldrich), and 28.8 μL of 4-tert-butylpyridine (Sigma-Aldrich) and 17.5 μL of bis(trifluoromethane)sulfonimide lithium salt (Sigma-Aldrich) in acetonitrile (520 mg mL\textsuperscript{-1}) were added as additives. The solution was spin-coated on the substrate, and finally 100-nm thick Au electrode was thermally evaporated.

**Encapsulation:** Fabricated device was sealed with encapsulation glass (AMG) by attaching getter (HD-S071313W-48; AD TECH) and dispensing the epoxy (XNR5570; Nagase) on an edge of the encapsulation glass. UV-curing (OmniScience) system was applied for 10 min to an epoxy to complete the glass encapsulation.

**Characterization:** FTIR (Nicolet iS50; Thermo Fisher) was conducted to characterize the organic bonding nature of the perovskite. Phases of the synthesized samples were characterized by XRD (D8 Advance; Scientific). The field-emission scanning electron microscope (FE-SEM; Merlin-Compact; Carl Zeiss) was used to observe the morphologies of alloyed perovskite. Work function and VBM of perovskite films were measured via multipurpose x-ray photoelectron spectroscopy (XPS; Sigma Probe; Thermo VG Scientific), conducted with argon
sputtering, and photon energy of $h\nu = 21.22$ eV was used in the ultraviolet photoelectron spectroscopy (UPS) measurement. Optical properties of the perovskite films were measured with UV-vis spectroscopy (V-770; JASCO) with an integrating sphere. PL (FlouTime300; PicoQuant) was conducted to understand the carrier recombination. Incident photon to current efficiency (IPCE) measurements were performed by solar cell IPCE system (K3100; McScience). For impedance analysis, a potentiostat (Zive SP-1; WonA Tech) was adopted, and the impedance of photovoltaic device was measured with 10 mV AC perturbation in the frequency range from 10 mHz to 100 kHz under zero bias in dark condition. Photocurrent density-voltage ($J-V$) curves were achieved via solar cell measurement system (K-3000; McScience) for an active area of 0.09 cm$^2$. 
6.3. Results and Discussion

Concerns regarding the perovskite stability are widely discussed in the solar-cell field, and it is realized that the perovskite layer plays a critical role for the degradation of devices [5,21-25,49-51]. The major degradation sources of the perovskite are organic species of the cations which degrade under humidity, heat and light, and further modification of such species is required to design more practical perovskite materials [21-25,47]. 1,2,4-triazole has triamine-based aromatic structure, and it possibly allows a strong interaction within the lattice as well as the energy minimization by the tilting behavior of an organic cation, leading to the structural stabilization [5,51-53]. Also, orientation of amine groups in 1,2,4-triazole tends to make them repel one another, resulting in a reduced dipole moment compared with the 1,2,3-triazole or imidazole, obtaining strong advantages over different multiamine-based ring-shaped molecules [54-57]. The low dipole moment reduces the reactivity with water, guaranteeing the high stability under the humid condition. Furthermore, 1,2,4-triazole is less volatile species than imidazole, MA or FA, making it the ideal stabilizer for the perovskite solute under the operating conditions [58,59].

Figure 6-1(a) illustrates the schematics of 1,2,4-triazole alloying in triple-cation perovskite. By analyzing the 1,2,4-triazole-alloyed perovskite film, x-ray diffraction (XRD) shows (110) peak shift towards lower angle and (224) and (314) peaks to the opposite direction, due to the transition into tetragonal phase by the 1,2,4-triazole solute in a triple-cation perovskite (Fig. 6-1(b)). When the solute is added up to 6%, a PbI₂ peak is observed with the reduced peak intensities of triple-cation perovskite, indicating the structural instability by excessive alloying (Fig. 6-
In order to advocate the phenomena, tolerance factor is calculated to be ~1.01 for the 6% alloying (values between 0.9 - 1.0 as a stable structure) [19,48]. To identify the molecular structure of 1,2,4-triazole solute in the perovskite, Fourier-transform infrared (FTIR) analysis is further conducted for the alloyed perovskite film (Fig. 6-1(c)), where a clear peak of N=N in ~1600 cm\(^{-1}\) can be seen after the incorporation of aromatic cations (raw data presented in Fig. 6-2(b)).

Aside from the lattice change, film morphologies are also analyzed to address the advantages of 1,2,4-triazole alloying. As shown in Fig. 6-3(a), 2% and 4% alloys exhibit uniformly sized grains, where 0% and 6% show multiple-size distributions which may be the imperfect grains or PbI\(_2\), respectively. In Fig. 6-3(b), the root-mean-square (rms) roughnesses and conductivities of perovskite films are addressed, confirming that the proper alloying in perovskite increases the quality of the perovskite films by the lattice stabilization. Topological images from the atomic-force microscopy (AFM) and optical images are also presented in Figs. 6-4 and 6-5. It can be seen that 6% alloy exhibits the highest conductivity, and this value originate from the mixed conductivity of PbI\(_2\) and alloyed perovskite (Fig. 6-2(a)). However, the improved conductivity of 2% or 4% alloy originates from the substitution of triazole, which contains delocalized aromatic structure to transport the charge efficiently within the perovskite lattice, contributing to the improved optoelectronic properties of perovskite materials [5,45].

Defects and traps of materials significantly affect the ion diffusion as well as charge carrier dynamics within the device, and the analyses and understanding of these defect states are undoubtedly important to improve both the device performance and stability. In order to investigate the carrier dynamics and recombination behaviors in
the perovskite films, time-resolved photoluminescence (TRPL), photoluminescence (PL), and absorptance are measured. As shown in Fig. 6-6(a), the alloy with 2% of 1,2,4-triazole exhibits the longest carrier lifetime, with the reduced traps expected. Interestingly, carrier lifetimes of 4% and 6% alloys are observed to be shorter than that of the bare perovskite, indicating the excessive alloying destabilizes the perovskite lattice. To further obtain the insights, absorption coefficients and steady-state PL are measured, with the 2% alloy exhibiting the lowest defects with the highest absorption and PL intensities (evidences for the strong excitation and radiative recombination, respectively). However, the PL of bare and 4% alloys are red shifted, indicating that the shallow traps are reduced in the 2% alloy (with small changes in the bandgap, as illustrated in Fig. 6-7(a)). Comparison of PL and bandgap indicates the modified traps at the shallow level, which can be highly influenced by the quality of perovskite and interfaces. Perovskite with 6% alloying forms PbI₂ (Fig. 6-2(a)), which ruins the proper recombination and weakens the optoelectronic properties. Based on the measured work function and valance band maximum (VBM) with the bandgap energy, the band structure of perovskite with proper 2% alloying is moving towards \textit{n}-type, thereby enhancing the electron transport (Figs. 6-6(b) and 6-7(b)). However, excessive alloying is not proper due to the lattice defects, making the light absorber less \textit{n}-type and leading to an ineffective charge transport for the device performance.
Fig. 6-1. Schematics and characterization of perovskite films. (a) Illustration for 1,2,4-triazole alloying in the triple-cation perovskite, and (b) the observed peak shift in XRD by alloying process. (c) Typical functional groups (C=N and N=N) in the 1,2,4-triazole alloyed perovskite by FTIR analysis.
Fig. 6-2. Characterization of perovskite films. (a) XRD with the ITO peak to confirm the clear peak shifting due to the alloying (Fig. 6-1(b)). (b) FTIR exhibiting the reduced N-H bonding by 1,2,4-triazole (Fig. 6-1(c)).
Fig. 6-3. Morphological and electrical characteristics of perovskite films. (a) SEM images of the 1,2,4-triazole-alloyed perovskite. (b) Film roughness and conductivity of 1,2,4-triazole-alloyed perovskite, as measured by AFM and 4-point probe. The 6%-alloyed film exhibits PbI$_2$ phase, leading to high roughness and conductivity.
Fig. 6-4. Roughness of perovskite films. Topology of bare and 1,2,4-triazole-alloyed perovskite films.
Fig. 6-5. Optical images of bare and 1,2,4-triazole-alloyed perovskite.
Fig. 6-6. Carrier and optoelectronic properties of perovskite films. (a) Carrier lifetime of 1,2,4-triazole-alloyed perovskite: TRPL, PL data, and bandgap determination by \((ahv)^2\) vs. \(hv\). (b) Electronic structures of 1,2,4-triazole-alloyed perovskite by UPS: work function and VBM.
Fig. 6-7. Changes in the (a) bandgap and (b) VBM of 1,2,4-triazole-alloyed perovskite.
To further explicate the characteristics of charge carriers and electronic structures, the electronic traps of the devices with various 1,2,4-triazole alloy contents are quantitatively analyzed. It is known that various phenomena including carrier accumulation and charging/discharging of electronic traps contribute to the capacitive feature of the device, and therefore a proper interpretation of the device capacitance can elucidate its defective characteristics in a perovskite solar cell [60-66]. The capacitance of a device is obtained from the impedance spectroscopy, and capacitance vs. frequency (C-f) is plotted in Fig. 6-8(a). While the capacitances of various alloys are all identical at high-frequency region, the low-frequency capacitances show differences indicating that the electronic trap states change by the addition of 1,2,4-triazole. For further understanding, deep-trap density is calculated from the C-f plot, and the distribution of trap states is depicted in Fig. 6-8(b) [17,67]. The 2%-alloyed device exhibits trap states shifting toward the bandedge plus reduced trap density compared to the bare-, 4%-, and 6%- alloyed perovskite solar cells, rationalizing its improved carrier transport observed by PL analysis. The shallow traps of 2% alloy possibly reduce the carrier recombination and provide facile charge transfer to the carrier-transport materials (SnO$_2$ and spiro-OMeTAD for electrons and holes, respectively). Schematics for carrier dynamics at the interfaces are drawn in Fig. 6-8(c) with the considerations of band diagram (from Figs. 6-6 and 6-7).

The photovoltaic performances of solar cells are illustrated in Fig. 6-9(a) and Table 6-1. While devices with 2% alloy exhibits the highest efficiencies with low hysteresis, devices with 4% and 6% alloys result in low reproducibility (Fig. S5) due
to the high concentration of deep-level defects and impurities (Figs. 6-2, 6-3, and 6-8). Steady-state current and external quantum efficiency (EQE) are also shown (Figs. 6-9(b) and (c)), where the 2%-alloyed device exhibits stable current up to 1000 s with the highest EQE. TRPL is once more conducted in SnO$_2$/perovskite/spiro-OMeTAD structure (Fig. 6-9(d)) to confirm how well carriers are transferable. The tendencies are well matched with the performance of perovskite solar cells, exhibiting that the 2%-alloyed perovskite is the optimum light-absorber material for the device efficiency.

Lastly, to evaluate the effect of 1,2,4-triazole on the stability of the device, the alloyed perovskite solar cells are compared with the bare device under the extreme condition (85°C/85% RH). While the perovskite solar cell without alloying sustains 90% of initial PCE for ~200 h (Fig. 6-11), 2%-alloyed perovskite solar cell sustains 90% PCE for more than 700 h, leading to a potential for the ultrastable perovskite materials. Thermally stable photovoltaic device is enabled thanks to the improved structural stability and passivated defects of 2%-alloyed perovskite, whereas 4%- and 6%- alloyed ones possess structural instability and deteriorative defect/trap characteristics as observed in this study.
Fig. 6-8. Electronic-trap states of perovskite films. (a) Capacitance-frequency plot and (b) trap-distribution spectra of solar cells with the 1,2,4-triazole-alloyed perovskite. (c) Schematic illustration for the band diagram and trap state in the device.
Fig. 6-9. Photovoltaic performance of perovskite solar cells. (a) J-V curves (scan rate: 10 mV s\(^{-1}\)), (b) steady-state current for 1000 s, and (c) EQE spectra for the bare and 1,2,4-triazole-alloyed perovskite solar cells. (d) TRPL spectra with the bare and 1,2,4-triazole-alloyed perovskite (FTO/\(\text{SnO}_2\)/perovskite/spiro-OMeTAD).
<table>
<thead>
<tr>
<th>Triazole Content</th>
<th>$J_{sc}$ (mA cm$^2$)</th>
<th>$V_{sc}$ (Voltage)</th>
<th>FF (%)</th>
<th>$\eta$ (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>0 % (rev.)</td>
<td>23.2</td>
<td>1.07</td>
<td>0.76</td>
<td>18.9 (17.0 ± 1.2)</td>
</tr>
<tr>
<td>0 % (for.)</td>
<td>23.5</td>
<td>1.05</td>
<td>0.74</td>
<td>18.4 (16.8 ± 1.0)</td>
</tr>
<tr>
<td>2 % (rev.)</td>
<td>24.4</td>
<td>1.09</td>
<td>0.79</td>
<td>20.9 (19.1 ± 1.1)</td>
</tr>
<tr>
<td>2 % (for.)</td>
<td>24.4</td>
<td>1.08</td>
<td>0.74</td>
<td>19.6 (18.3 ± 1.0)</td>
</tr>
<tr>
<td>4 % (rev.)</td>
<td>21.7</td>
<td>1.03</td>
<td>0.67</td>
<td>15.0 (12.4 ± 1.8)</td>
</tr>
<tr>
<td>4 % (for.)</td>
<td>21.3</td>
<td>0.99</td>
<td>0.61</td>
<td>12.9 (10.8 ± 1.4)</td>
</tr>
<tr>
<td>6 % (rev.)</td>
<td>21.0</td>
<td>1.00</td>
<td>0.67</td>
<td>14.2 (10.4 ± 2.7)</td>
</tr>
<tr>
<td>6 % (for.)</td>
<td>21.0</td>
<td>1.01</td>
<td>0.40</td>
<td>8.60 (6.3 ± 2.2)</td>
</tr>
</tbody>
</table>

Table 6-1. The highest and average values of the device performance. Photovoltaic performance of perovskite solar cells with 1,2,4-triazole alloyed.
Fig. 6-10. Device reproducibility of bare and 1,2,4-triazole-alloyed perovskite.
Fig. 6-11. Device stability under 85°C/85% RH environment (encapsulated).
6.4. Conclusions

Obtaining high PCE and stability for the perovskite solar cells are the major bottlenecks for commercialization. Even though the triple-cation perovskite is well known for its stability, reactive species and weak bonding sites of organic cations (MA and FA) still provide rooms for the further improvement. Herein, we have alloyed 1,2,4-triazole as a cation solute in perovskite to minimize defects and thereby enhance the optoelectronic properties of perovskite, leading to the achievement of superior performance and stability under extreme conditions. To satisfy the structural stabilization, the addition of 1,2,4-triazole is optimally controlled, and the devices with 2%-alloyed perovskite exhibits the PCE of 20.9% with the superior stability compared with the device without solute. These straightforward and novel strategies can support further development for the perovskite research and practical commercialization.
6.5. References


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bonding interaction in the prototypic hybrid halide perovskite, tetragonal 

and Dipole Moment of 1,2,4-Triazole: Identification of Tautomer in Vapour Phase,”


Appendix: List of Publications and Presentations

A.1. Publications (International)

1. “Triamine-Based Aromatic Cation as a Novel Stabilizer for Efficient Perovskite Solar Cells”
   Jinhyun Kim, Alan Jiwan Yun, Bumjin Gil, Younghyun Lee, and Byungwoo Park*

2. “Interfacial Modification and Defect Passivation by Crosslinking Interlayer with Realization of Efficient and Stable CuSCN-Based Perovskite Solar Cell”
   Jinhyun Kim,† Younghyun Lee,† Alan Jiwan Yun,† Bumjin Gil, and Byungwoo Park*

   Alan Jiwan Yun,† Jinhyun Kim,† Taehyun Hwang, and Byungwoo Park*

4. "An Aromatic Diamine Molecule as the A-Site Solute for Highly Durable and Efficient Perovskite Solar Cells"
   Jinhyun Kim, Taehyun Hwang, Byungho Lee, Sangheon Lee, Kimin Park, Helen Hejin Park, and Byungwoo Park*
   *Small Methods* 3, 1800361 (2019). [Front Cover]
5. "From Nanostructural Evolution to Dynamic Interplay of Constituents: Perspectives for Perovskite Solar Cells"

Taehyun Hwang,† Byungho Lee,† Jinhyun Kim,† Sangheon Lee,† Bumjin Gil, Alan Jiwan Yun, and Byungwoo Park*  


Jinhyun Kim, Taehyun Hwang, Sangheon Lee, Byungho Lee, Jaewon Kim, Jaewook Kim, Bumjin Gil, and Byungwoo Park*  

7. "Solvent and Intermediate Phase as Boosters for the Perovskite Transformation and Solar Cell Performance"

Jinhyun Kim, Taehyun Hwang, Sangheon Lee, Byungho Lee, Jaewon Kim, Gil Su Jang, Seunghoon Nam, and Byungwoo Park*  

8. "Electronic Traps and Their Correlations to Perovskite Solar Cell Performance via Compositional and Thermal Annealing Controls"

Taehyun Hwang, Alan Jiwan Yun, Jinhyun Kim, Duckhyung Cho, Sangyeon Kim, Seunghun Hong, and Byungwoo Park*  

9. "Complementary Surface Modification by Disordered Carbon and Reduced Graphene Oxide on SnO₂ Hollow Spheres as an Anode for Li-Ion Battery"

Hyungsub Woo, Sungun Wi, Jaewon Kim, Jinhyun Kim, Sangheon Lee, Taehyun Hwang, Joonhyeon Kang, Jaewook Kim, Kimin Park, Bumjin Gil,
Seunghoon Nam,* and Byungwoo Park*

10. "Evaluating the Optoelectronic Quality of Hybrid Perovskites by Conductive Atomic Force Microscopy with Noise Spectroscopy"
Byungho Lee, Sangheon Lee, Duckhyung Cho, Jinhyun Kim, Taehyun Hwang, Kyung Hwan Kim, Seunghun Hong,* Taeho Moon,* and Byungwoo Park*

11. "Investigation of Chlorine-Mediated Microstructural Evolution of CH$_3$NH$_3$PbI$_3$(Cl) Grains for High Optoelectronic Responses"
Taehyun Hwang, Duckhyung Cho, Jinhyun Kim, Jaewon Kim, Sangheon Lee, Byungho Lee, Kyung Hwan Kim, Seunghun Hong, Chunjoong Kim, and Byungwoo Park*

12. "Integration of CdSe/CdSe$_{1-x}$Te$_x$ Type-II Heterojunction Nanorods into Hierarchically Porous TiO$_2$ Electrode for Efficient Solar Energy Conversion"
Sangheon Lee,* Joseph C. Flanagan,* Joonhyeon Kang, Jinhyun Kim, Moonsub Shim,* and Byungwoo Park*

13. "Organic-Acid Texturing of Transparent Electrodes Toward Broadband Light Trapping in Thin-Film Solar Cells"
Woojin Lee, Taehyun Hwang, Sangheon Lee, Seung-Yoon Lee, Joonhyeon Kang, Byungho Lee, Jinhyun Kim, Taeho Moon,* and Byungwoo Park*
14. "Facile Conversion Synthesis of Densely-Formed Branched ZnO-Nanowire Arrays for Quantum-Dot-Sensitized Solar Cells"
Woojin Lee, Suji Kang, Taehyun Hwang, Kunsu Kim, Hyungsub Woo, Byungho Lee, Jaewon Kim, Jinhyun Kim, and Byungwoo Park*

15. "Nanoroughness Control of Al-Doped ZnO for High Efficiency Si Thin-Film Solar Cells"
Seung-Yoon Lee, Taehyun Hwang, Sangheon Lee, Woojin Lee, Byungho Lee, Jinhyun Kim, Soohyun Kim, Hyun Lee, Heon-Min Lee, and Byungwoo Park*

16. "Improving Scattering Layer through Mixture of Nanoporous Spheres and Nanoparticles in ZnO-Based Dye-Sensitized Solar Cells"
Chohui Kim, Hongsik Choi, Jae Il Kim, Sangheon Lee, Jinhyun Kim, Woojin Lee, Taehyun Hwang, Suji Kang, Taeho Moon,* and Byungwoo Park*
A.1. Presentations (International and Domestic)

   Alan Jiwan Yun, Jinhyun Kim, Taehyun Hwang, Byungwoo Park

2. "Unraveling the Origins that Enable Efficient Perovskite Solar Cells: Influence of Thermal Annealing via Temporal Evaluation"
   Taehyun Hwang, Byungho Lee, Sangheon Lee, Jinhyun Kim, Bumjin Gil, Alan Jiwan Yun, and Byungwoo Park

3. "Imidazole as a Cation-Dopant for Stable and Efficient Perovskite Solar Cells"
   Jinhyun Kim, Taehyun Hwang, Byungho Lee, Sangheon Lee, Bumjin Gil, Kimin Park, and Byungwoo Park

4. "Organometallic Perovskite Synthesis for Efficient and Stable Perovskite Solar Cells"
   Jinhyun Kim, Taehyun Hwang, Sangheon Lee, Byungho Lee, Jaewon Kim, and Byungwoo Park
5. "Integration of II-VI Nanorods in Sensitized Photovoltaics via Open-Structured Photoanode and Co-Sensitization Strategy"
   Sangheon Lee, Joseph C. Flanagan, Joonhyeon Kang, Jinhyun Kim, Moonsub Shim, and Byungwoo Park

6. "Organometallic Perovskite Synthesis for Efficient and Stable Perovskite Solar Cells"
   Jinhyun Kim, Taehyun Hwang, Sangheon Lee, Byungho Lee, Jaewon Kim, and Byungwoo Park
   *International Conference on Electronic Materials and Nanotechnology for Green Environment (ENGE2016).* Jeju, Korea, November 6-9, 2016. [Poster by Jinhyun Kim]

7. "Investigation of Chlorine-Mediated Microstructural Evolution of CH$_3$NH$_3$PbI$_3$(Cl) for Enabling High Performance Solar Cell"
   Taehyun Hwang, Duckhyung Cho, Jinhyun Kim, Jaewon Kim, Sangheon Lee, Byungho Lee, Kyung Hwan Kim, Seunghun Hong, and Byungwoo Park
   *International Conference on Electronic Materials and Nanotechnology for Green Environment (ENGE2016).* Jeju, Korea, November 6-9, 2016.

8. "Integration of II-VI Nanorods in Sensitized Photovoltaics via Open-Structured Photoanode and Co-Sensitization Strategy"
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9. "Integration of CdSe/CdSe\textsubscript{1-x}Te\textsubscript{x} Type-II Heterojunction Nanorods into Hierarchically Porous TiO\textsubscript{2} Electrode for Efficient Solar Energy Conversion"

Sangheon Lee, Joseph C. Flanagan, Joonhyeon Kang, Jinhyun Kim, Moonsub Shim, and Byungwoo Park

국문초록

에너지 소비는 대표적으로 화석연료, 석유화학, 핵 발전에 의존되어 왔다. 본 에너지들은 지구온난화와 핵폐기물 등, 인류의 안전을 위협하고 있다. 자원적으로써, 재생에너지가 현재 에너지생산을 대체하고 있는 추세이나 공급량에 못 미치는 실정이다. 태양전지는 임시 광을 전기로 변환시켜주는 에너지 발전장치로서, 환경적 문제없이 에너지를 공급해줄 수 있는 촉망 받는 해결책이라고 할 수 있다. 태양전지를 에너지 시장에서 경쟁력을 갖게 하기 위해, 저비용에서의 높은 광 전환효율과 함께 높은 내구성을 포함하고 있어야 한다. 더 나아가, 웨어러블 기기와 같이 생활에&R에서 밀접할 수 있도록 적용 가능해야 한다. 그리므로 태양전지의 넓은 상용화를 위해서, 물질과 소자에 대한 과학적인 이해와 발전이 필요하다.

연구진들은 태양전지의 잠재성을 끌어내기 위하여 다양한 물질 및 소자 구조들을 탐구해 왔다. 특히, 광전특성이 뛰어난 박막반도체 물질을 태양전지에 적용시키는 방향이 널리 탐구 되었다. 그 중에서도, 유무기 페로브스카이트는 우수한 밴드갭, 확산거리, 흡수계수의 본연의 우수한 특성들로 인해 많은 주목을 받았다. 더 나아가 합성 및 공정의 간편함과 저비용에 있어서 대량생산에서 강한 이점을 지니고 있다. 하지만, 유무기 페로브스카이트에서의 유기물은 (methylammonium (MA) 또는 formamidinium (FA)) 외부 열, 빛, 수분에 높은 반응성을 가지고 있어서, 실생활에서의 적용이 어려운 실정이다. 유무기 페로브스카이트의 문제 이외에도, 소자 내에서의 전자 및 정공

230

국문 초록
전달물질은 가격이 높고 복잡한 공정을 요구하므로 유무기 페로브스카이트 태양전지의 상용화에 걸림돌이 되고 있다. 그러므로 현재의 한계를 뛰어넘기 위한 물질 및 소자의 추가적인 연구가 요구되어야 한다.

1장에서는 유무기 페로브스카이트와 태양전지의 기초적인 이해를 돕기 위한 개요를 할 것이다. 이는 물리화학적 접근에 의거한 소재 이론 및 태양전지의 작동원리를 다루고 동시에, 태양전지의 광전특성을 향상시키기 위한 선행 연구들을 잡고 넘어가고자 한다. 더 나아가, 물질 및 소자의 분해이론과 이를 해결하기 위한 선행연구 되었던 해결 방안을 소개함으로써 유무기 페로브스카이트 연구분야를 이해하고자 한다.

2장에서는 페로브스카이트 태양전지의 이상적인 공정과 합성을 다루고자 한다. 2014년, 염소가 도핑된 페로브스카이트는 격자구조내의 패시베이션 효과로 많은 주목을 받아왔다. 이로 인하여, 염소 도핑은 성능향상과 안정성을 모두 올리주는 방법으로 여겨져 왔다. 하지만, 이를 합성하기 위한 화학적 이해는 미미하게 이루어져 왔고, 이를 이해하면 추가적인 최적화를 할 수 있는 가능성을 지니고 있다. 염소가 도핑된 페로브스카이트의 반응과정을 이해하기 위해, 다양한 공정과 합성법을 2장에서 구체적으로 다루었다. 결론적으로, 반응의 정도를 조절하는 기술을 합여하여 반응 과정중의 중간상을 발견하는데 성공하였고, 이를 공학적으로 응용하여 극도로 안정한 페로브스카이트를 만드는데 성공하였다. 최종적으로, 이를 페로브스카이트 태양전지에 응용하여 안정적이고 고효율을 내는 소자를 만드는 방법을 논하고자

231

국문 초록

서울대학교
3장에서는 전자전달물질의 합성과 공정을 다루고자 한다. 금속산화물은 전자전달물질로 널리 이용되어왔으며, 높은 수준의 박막을 얻기 위하여 복잡한 공정들을 요구로 한다. 대표적으로 전공공정 또는 용액공정을 이용하여 전자전달층을 투명전극 위에 쌓아 한다. 그러나 각각의 방법에는 질 높은 박막을 형성하는데 문제를 가지고 있다. 또한 이러한 박막의 질은 상단에 쌓이 될 페로브스카이트의 형성에도 영향을 준다. 그러므로 용액공정과 전공공정을 융합하여 단점을 보완하고 소자의 성능을 향상시키는 이상적인 전자전달층 제작법을 소개하고자 한다.

4장에서는 페로브스카이트의 분해과정을 관찰하는 내용을 다루고자 한다. 페로브스카이트 내부의 유기물부분은 페로브스카이트의 분해를 중점적으로 일으키는 부분으로 알려져 있고, 이를 분석하고 보완하는 방법론에 대해 공부해 보았다. 또한 새로운 페로브스카이트 디자인을 통한 광전특성 향상을 원리나 다뤄보고자 한다. 대표적으로, 다양한 아민 개수의 방향족유기물을 이상적으로 활용하여 페로브스카이트의 유기 부분에 치환하였다. 방향족유기물의 구조특수성은 비편재화된 파이 결합으로 인해 소재 및 소자의 광전특성과 안정성을 기하급수적으로 향상시켰다. 더 나아가, 소재 이론 및 디자인 방법론 등을 소개하고자 한다.

5장에서는, 전자전달물질의 안정성 및 비용적인 측면을 다루고자 한다. 대부분의 상황에서는, 금속산화물은 광촉매반응을 가지고 있으며, 이는 페로브스카이트와의 분해반응을 일으켜 낮은 소자
안정성을 가지게 된다. 그러므로, 안정적이고 효율적인 전자전달물질을 만드는 방법론에 대해 설명하고자 한다. 더 나아가, 전자전도도를 얻기 위한 금속산화물의 고온합성은 제조단가를 높이는 문제가기도 한다. 결과적으로, 저온에서 합성가능하고 안정하면서도 고효율을 소자를 만드는 방법론을 다루고자 한다.

6장에서는 페로브스카이트의 화학적인 요소들을 향상시키기 위한 복합적인 전략을 소개하고자 한다. 페로브스카이트는 유기물, 전이금속, 그리고 할로겐으로 이루어져있고, 유기물이 대표적으로 낮은 안정성을 가지고 있다. 유기물은 페로브스카이트 격자구조 내에 수소결합을 하고 있으며, 이는 극성성질을 띄는 외부환경과 높은 반응성을 가지고 있다. 그러므로 이러한 화학결합을 제어하기 위한 금속 그리고 저극성 유기물을 복합적으로 응용하여 소재를 안정화시키는 방법을 논하고자 한다. 안정화 과정을 진행함과 동시에, 광전기적 특성 및 열역학적 변화를 관찰하고 소자에서의 성능 및 안정성 향상을 추가적으로 관찰하고자 한다.

주요어: 햇빛전지, 유무기 페로브스카이트, 조성공학, 용매, 양이온, 음이온, 전자전달물질, 정공전달물질, 안정성, 고분자, 금속산화물, 복합물질, 중착공정, 재결합, 결합, 전기적 트랩.

학번: 2013-23817
감사의 글

2013년 연구실 생활을 시작하여 6년이란 시간이 빠르게 지났습니다. 수많은 일들이 있었고 그 속에서 이뤄낸 작은 결실들과 가르침들을 간직하고 새로운 곳에서 새로운 도전을 하고자 합니다. 긴 유학생생활 이후 익숙하지 않은 한국에서의 시간을 화려하고 가치 있게 만들어준 교수님, 연구실 선후배들, 그리고 수많은 고마운 분들께 감사의 글을 짏고자 합니다.

먼저 학위과정 동안 함께 연구자로써 성장할 수 있는 기회를 주신 박병우 교수님께 감사 드립니다. 연구에 대해 자유롭게 생각하고 토론할 수 있도록 기회를 마련해주신 교수님의 배려는 연구를 창의적으로 바라보는데 많은 도움이 되었습니다. 또한 제가 연구 및 생활에 지칠 때 매번 위로해주시며 저의 삶의 원동력을 되새기며 힘을 내 수 있게 해주었습니다. 자주 커피도 주시고 편하게 교수님과 소통할 수 있어서 대학원의 삶이 만족스러웠습니다.

제가 연구를 하면서 난관에 부딪치거나 조언을 구해야 할 때 아낌없이 도와주신 신병하교수님 그리고 대학원생분들 분께 이 자리를 빌어 전심으로 감사 드립니다. 다양한 의견과 해결책들을 나누며 지식적인 부분과 실험적인 부분들은 저를 더 뛰어난 연구자로 성장시켜주었습니다. 더불어 바쁘신 와중에 저희 학위논문 심사를 위해 귀한 시간을 내어주시고 조언을 주신 심사위원님들께도 감사 드립니다.

유기 및 고분자에 대한 깊은 이해를 많이 생각하고 논리를 펼칠 수 있게 도와주신 김장주교수님과 이태우교수님, 분야에 다양한 지식과 접근방법론을 심도 있게 생각할 수 있도록 조언해주신 김진영교수님과

234 감사의 글
신명하교수님. 분야의 전반적인 큰 틀에서 여러 계단음을 느끼게 해주셨던 김상범교수님의 조언들은 제가 학위를 마무리하는데 그리고 연구자가 되는데 있어서 큰 영향을 주었습니다.

학위 기간 동안 많은 도움을 주시고 즐거운 추억들을 함께 나누도록 도와주신 연구실 선후배님들께 감사의 말씀을 전합니다. 연구실 초기에 부족한 저를 도와주신 문태호 교수님과 남승훈 교수님, 깊은 경험과 지식에서 나오는 김천중 교수님과의 대화는 저를 즐겁게 분야에 대해 생각해보는 도전적인 자세를 느낄 수 있게 해주었습니다. 또한 따뜻한 인품과 유머로 항상 연구실의 생기를 넋어주셨던 재익이형과 꽁치형 그리고 연구실 초기에 가장 잘 쟁쟁한초회누나, 따뜻한 옷을 지어주시며 좋은 말 그리고 위로도 해주신 수지누나덕분에 많이 배우고 보람된 연구실생활을 시작할 수 있었습니다. 준현이형과는 같은 틀이 아닙니다만, 안에서 또는 밖에서 같이 연구실 및 인생에 대해 많은 얘기를 나누고 혼나면서 도전적인 실험정신 및 노력보단 성과라는 말을 가슴에 새기며 지낼 수 있도록 도와주셨습니다. 연구실에서 능률한 형이시가 따뜻하게 후배들을 아껴주셨던 성현이형을 보면서 본받을 점이 많다고 생각하였습니다. 항상 후배들의 연구 및 생활을 쟁취했던 좋은 추억들을 많이 추쳤습니다. 많이 바쁘셔서 자주 뵐지는 못했지만 항상 따뜻하게 해주셨던 송윤이형 그리고 논자시 및 강력한 정보력으로 저의 졸업도움 및 조언을 해주셨던 선배형께서도 깊은 감사의 인사를 드립니다. 폐로브스카이트 태양전지를 초기 때 시작하여 많은 난관에 봉착할 때 태현이형 그리고 병호형과 같이 의견들을 나누며 해결나갔습니다. 때로는 엄격한 선배였지만, 함께 연구하고 놀면서
연구를 발전시키는 길이 심심하지 않고 위안이 많이 되었습니다. 연구
이외에도 병호형과 태현이형에게는 감사하고 미안한 것도 많습니다.
제가 고집도 부리고 잘못된 행동이 있을 때 지적해주시며 더 좋은
연구자의 길로써 인도하심에 진심으로 감사 드립니다. 저랑 동갑이자
저의 선배인 상헌이에게도 많이 감사합니다. 열정만 가득하고 철없던
연구실 초기시절 항상 물어보면 친절하게 도와주고 의견도 내주면서
어떻게 보면 저보다 형 같은 구석이 많다고 느꼈습니다. 매번 사람들을
do우려는 착한 심성은 어딜 가든 좋은 결과를 낼 수 있으리라 장담하고
기원합니다. 형접이형과는 정말 많은 추억이 있었고 같이 여행도 가며
돈독한 우정을 지켜나갈 수 있었으나, 요새 많이 바쁘신 거 같아서
아쉽습니다. 인생에 대해서도 많은 얘기를 나누며 위로도 많이 해주시고
정신 없었던 학위과정 속에 너무도 감사한 사람이었습니다.
재원이형께서도 항상 돈독한 형처럼 대화하고 저의 고민 그리고
난관들을 들어주며 격려해주신 부분들이 많이 위안이 되었습니다.
어떻게 보면 저는 연구실에서 철없는 막내처럼 지내왔고 인격적으로
훌륭했었던 선배들 덕에 행복한 연구생활을 했다고 생각하고 아마
선배님들께서도 동의하실 거라 생각합니다. 막내의 생활을 즐기고 있을
때 후배들이 많이 들어왔습니다. 부지런하고 앞장서서 문제를 잘
해결해나가는 지원이, 성품이 바르고 열심히 하는 범진이, 돌발행동을
해서 당황스럽지만 마음만은 따뜻한 기민이, 그리고 지금까지 날 잘
따라와주고 믿어준 고마운 영현이에게 남은 연구실 생활을 즐겁고 잘
보내라는 말을 전합니다.

연구실 외에도 저에게 서울대학교에서의 삶은 감사한
부분들이 많았습니다. 연구실외에서도 연구적인 도움을 많이 받았고 서로 도우며 생각과 도전정신을 키워나갔습니다. 우선 신병하교수님 연구실의 김대한씨에게 이 자리를 빌려 감사의 인사 드립니다. 웃음을 항상 잃지 않으시면 최종할 정도로 저희에게 많은 도움을 주셨습니다. 또한 김대형교수님 연구실의 태규와 용찬이에게도 감사의 인사를 드립니다. 품미로 만나 페로브스카이트에 대해 아무것도 모르던 시절 같이 헤매고 의견 나누고 장비도 조금씩 써보고 많은 위안이 되었습니다. 또한 밖에서 보면서 참 좋은 사람이라는 것들을 많이 느꼈습니다. 이제는 페로브스카이트에 대해 심도 있는 대화를 할 수 있는 횟수는 줄어들겠지만, 풍ulous 동생 그리고 연구원으로서 마주하기를 바랍니다. 약 6년이란 시간 동안 새로 형성된 형 동생 친구들이 많습니다. 항상 심심한 밤이면 같이 한잔을 기울이며 인생 얘기 나누던 해성어형은 저에게 정말 고마운 존재입니다. 형의 인생관이나 순수한 열정 그리고 문제를 해결해나가는 말씀들을 들을 때 참으로 배울 점이 많은 사람이라는 걸 느꼈습니다. 그리고 너무도 즐겁게 형과 같이 여행도하고 놀았던 시간들은 제 대학원생활에 활력을 가득하여주었습니다. 학교를 떠나 이후에도 형과 함께 즐거운 추억들을 계속해서 만들어 나가고 싶습니다. 또한 병관이도 참으로 소중한 동생입니다. 항상 병관이랑 만나면 텐션도 울라가고 즐거웠습니다. 같이 있으면 치유 받는다는 느낌이 드는 저에게 굉장히 좋았던 사람입니다. 그 외에도 군대동기들, 서울대입구역에서의 감사한 사람들 등등 너무도 많은 사람들이 있지만, 항상 감사하고 소중했습니다. 언제나 즐겁고 행복하길 기원하고 그런 과정에 제가 함께하지 바랍니다.
중학교 때부터 유학을 가 한국에 중학교 고등학교 동창이 많이 있지는 않지만 이 자리로 빌어 소중한 친구들에게 감사하다는 말 하고 싶습니다. 알렉스는 고등학교 때부터 참 찌올라 붙어 지내던 친구였습니다. 친근한 우리들은 서로 틀어 맞으며 지금까지 왔지만, 고등학교 그리고 대학교에 있어서 찬으로 위안도 많이 되고 서로 잘 친구주는 축복의 길이 되었음에 감사하게 생각합니다. 또한 JD님의 근희 윤재와도 지금 다들 각자의 길에서 열심히 살고 있지만, 지금까지 제가 받아온 길에 많은 도움 그리고 격려가 되었습니다. 경환이는 회사에서 보게 될 테지만, 친구로 계미있는 추억들도 많았고 앞으로 즐기면서 나갈 미래가 기대가 됩니다.

마지막으로 박사학위를 받게 되는 지금까지 제가 걱정 없이 학업에만 전념할 수 있도록 지지해주신 부모님께 감사드립니다. 제가 이렇게 까지 할 수 있었음에도 친구들을 하고 중간에 수많은 난관들이 있었으나, 그럴 때마다 응원해주고 지지해주셔서 제가 잘 마무리 지었음에 의심하지 않습니다. 듣기 싫은 소리를 하셨을 때도 이 모든 것들이 저에 대한 걱정과 발전을 위해 하셨다는 것을 알고 있습니다. 또한 부모님께서 걱정하지 않으시기를 바라며 더 열심히 노력하기도 했던 것 같습니다. 지금까지 받아온 사랑과 지지, 앞으로 천천히 갈아나가도록 하겠습니다. 사랑합니다.

2019년 8월
김진현 드림

감사의 글